

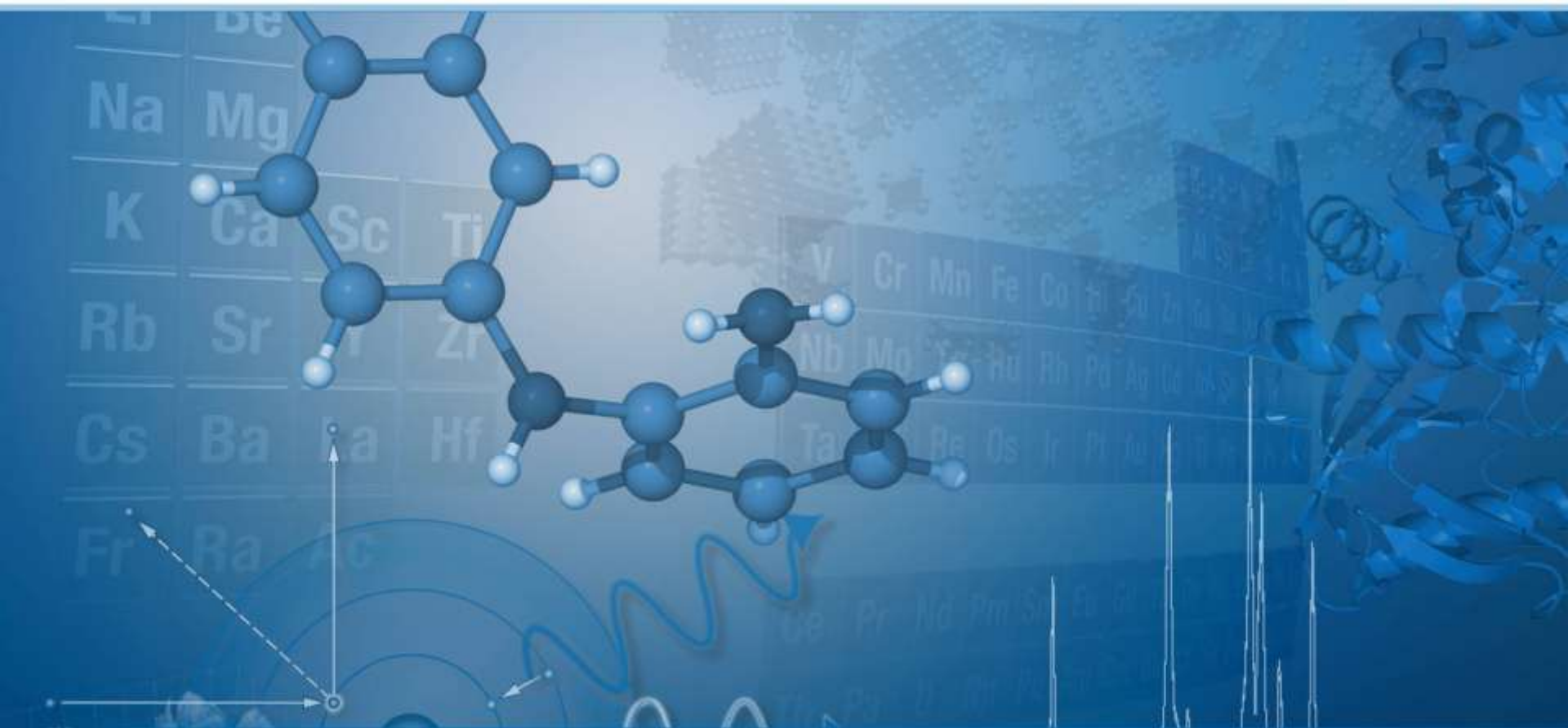
Good Diffraction Practice Webinar Series



High Resolution X-ray Diffractometry 2 – Reciprocal Space Mapping

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www.bruker-webinars.com



Welcome



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Outline

- What is Reciprocal Space
- What can be measured by Reciprocal Space maps (RSMs)
- How to measure RSMs
- RSMs with 1D-detectors
- RSMs with 2D-detectors

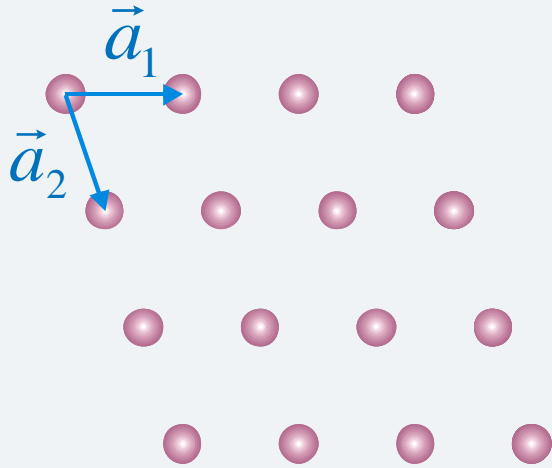
- **What is Reciprocal Space**
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Scattering from a crystal: The concept of reciprocal space



Real space

Crystal lattice



$$\vec{R} = n_1 \vec{a}_1 + n_2 \vec{a}_2 + n_3 \vec{a}_3$$

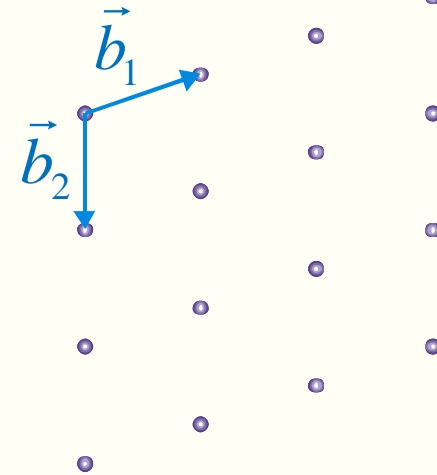
Fourier
transform

$$\vec{a}_i \cdot \vec{b}_k = 2\pi\delta_{ik}$$

$$\exp(i\vec{G}\vec{R}) = 1$$

q-space

Reciprocal lattice

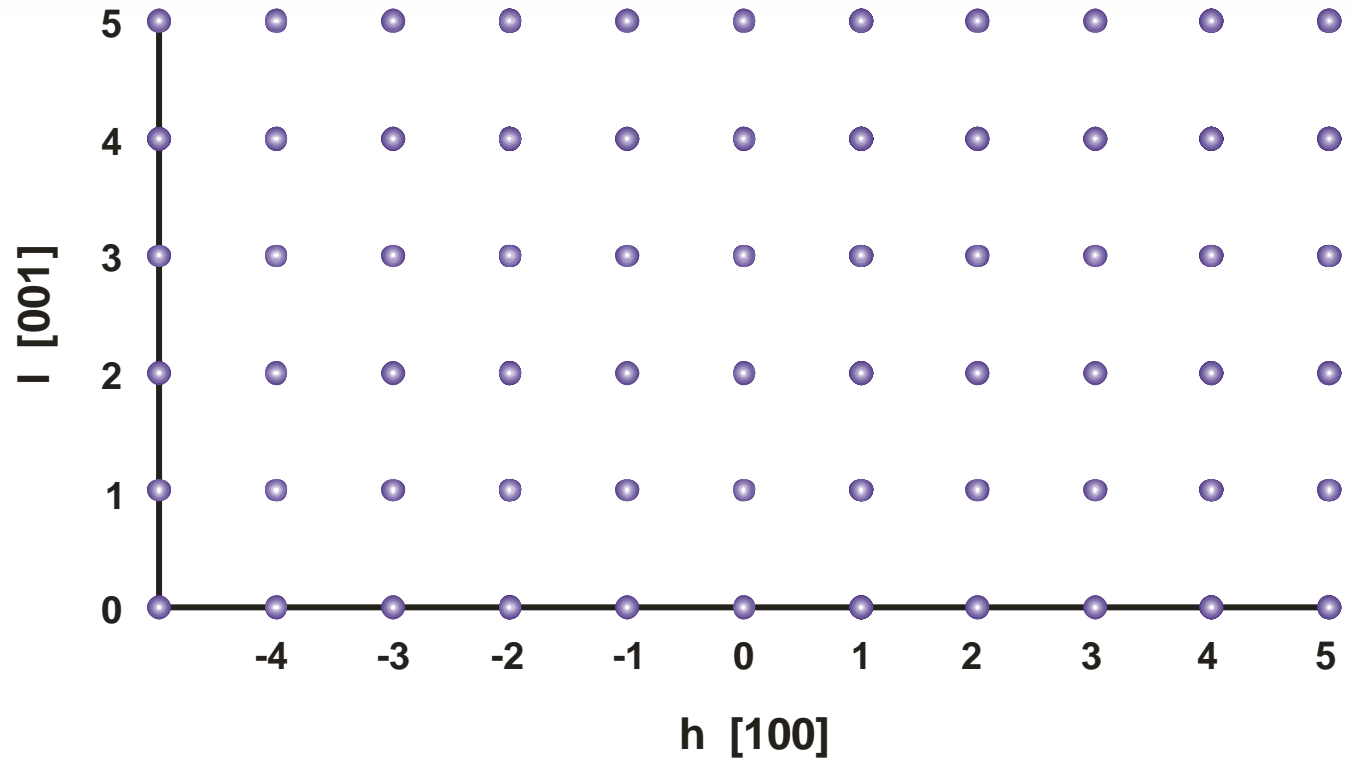
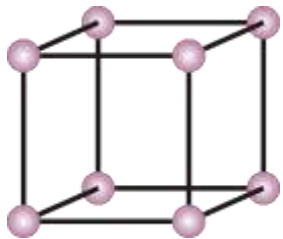


$$\vec{G} = h\vec{b}_1 + k\vec{b}_2 + l\vec{b}_3$$

Accessible region in reciprocal space – Experimental constraints



of a single atom
cubic crystal



Accessible region in reciprocal space - Wavelength

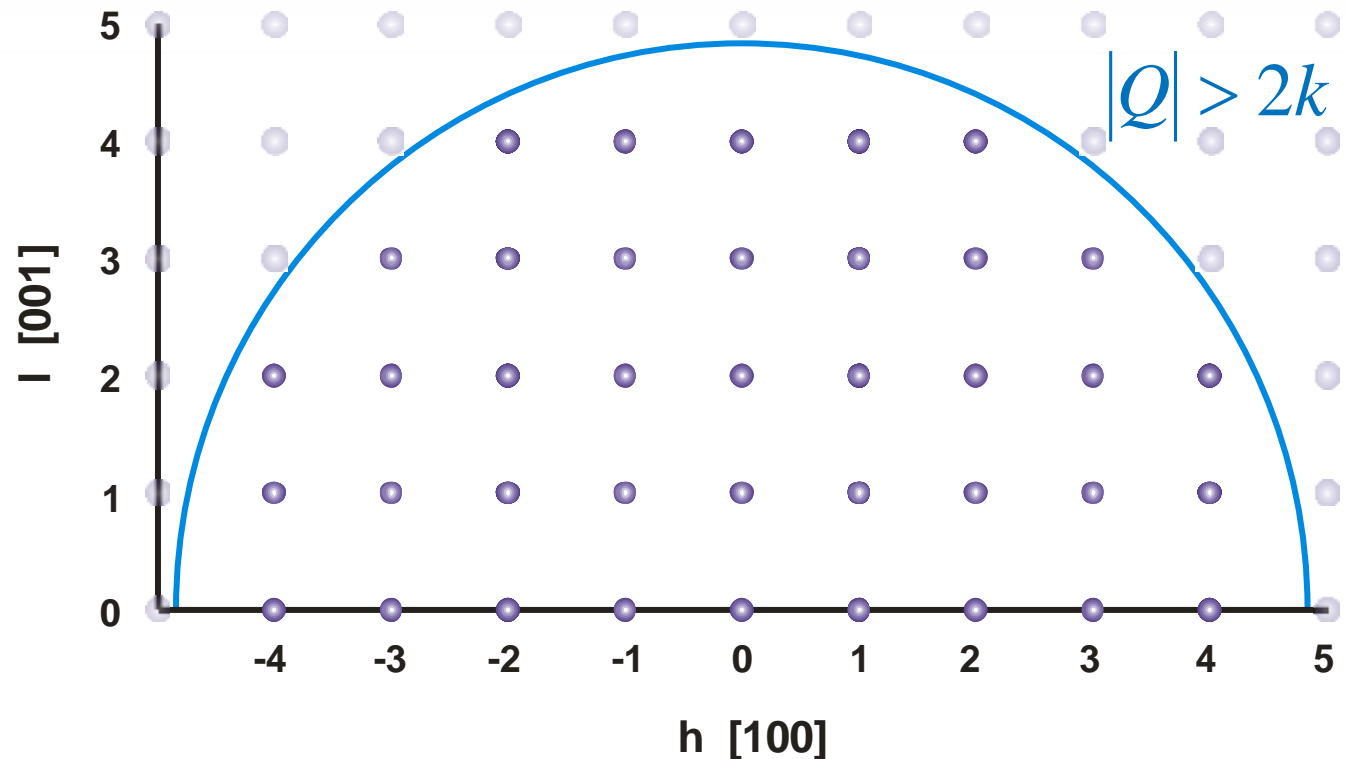


Wavevector

$$k = 2\pi / \lambda$$

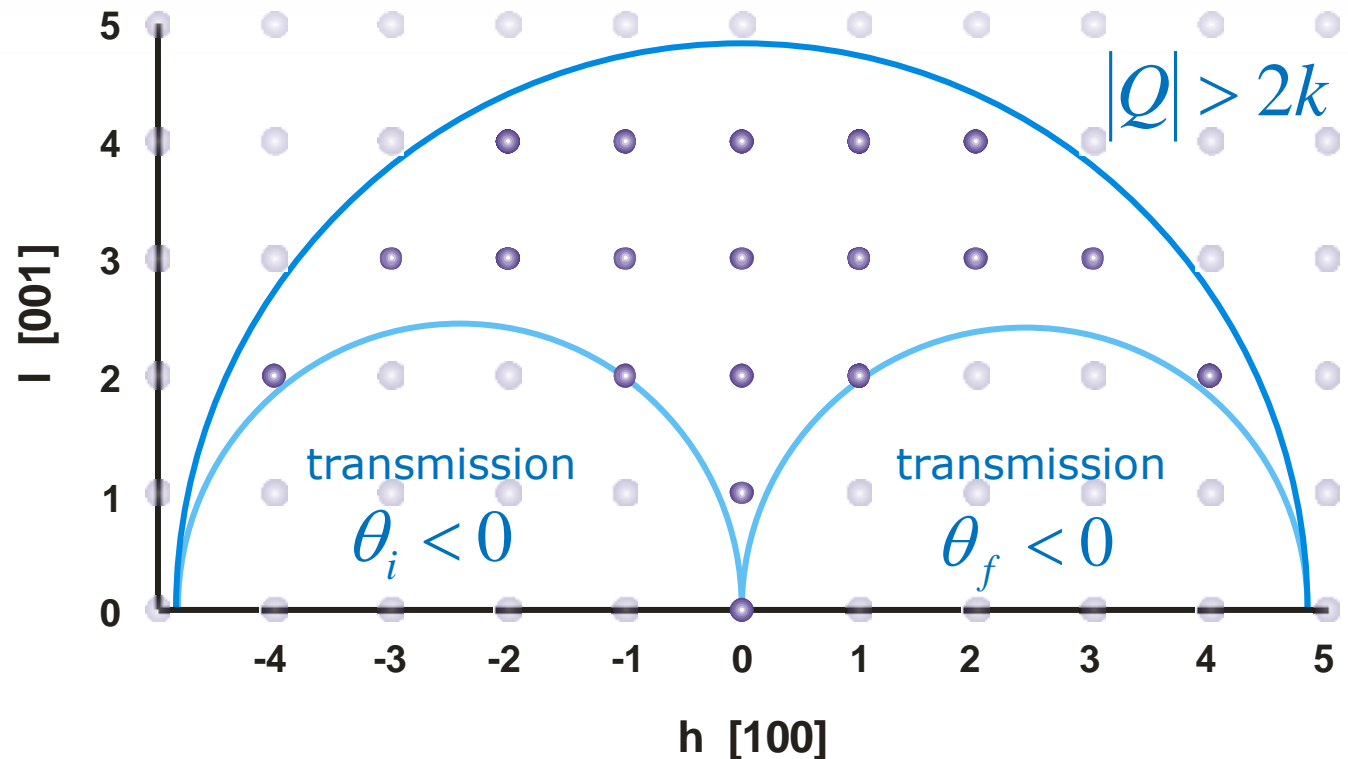
Wavelength

$$\lambda [nm] = \frac{1.24}{E [keV]}$$



The range of accessible reflections can be increased by using X-rays of a higher energy.

Accessible region in reciprocal space - Geometry

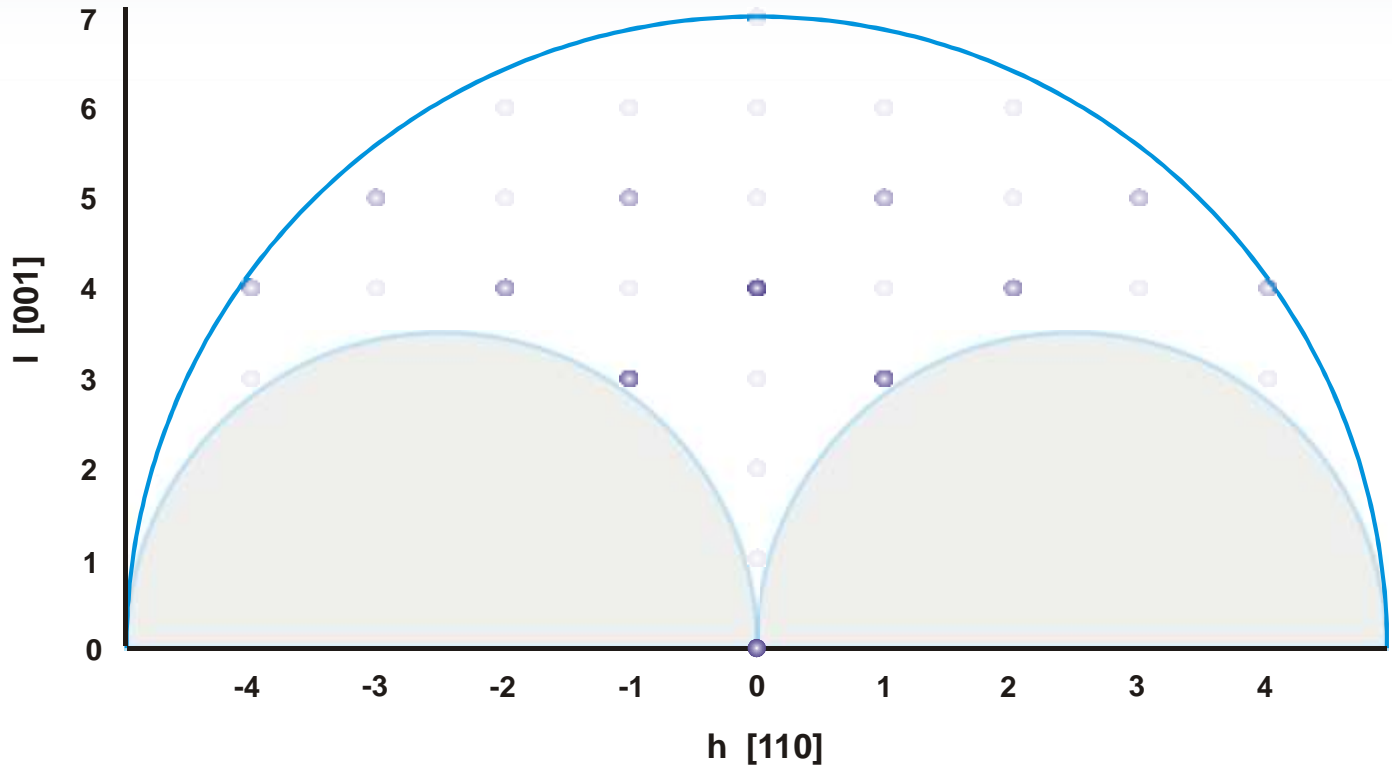
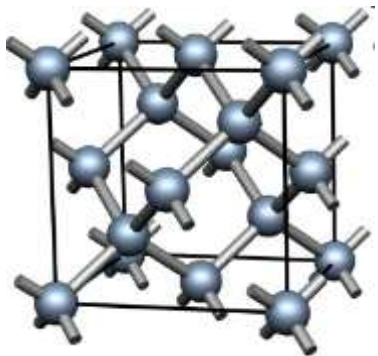


Reflections very close to the half-spheres have grazing incidence or grazing exit geometry \rightarrow surface sensitivity

A silicon crystal in reciprocal space – Structure Factor



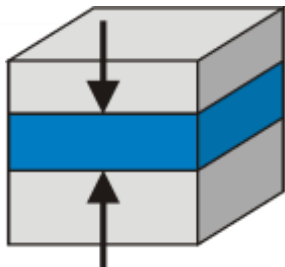
FCC-lattice with
Si atoms at
(0, 0, 0) and
($\frac{1}{4}$, $\frac{1}{4}$, $\frac{1}{4}$)



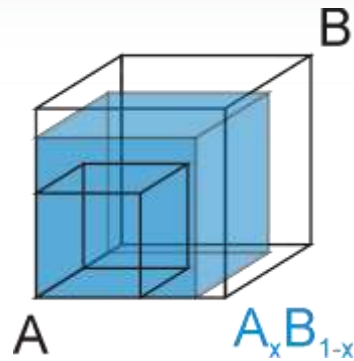
The structure factor of the crystal determines the scattered intensity.

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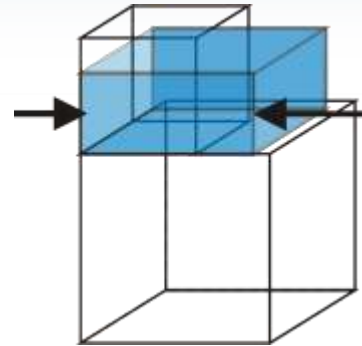
Analytical tasks



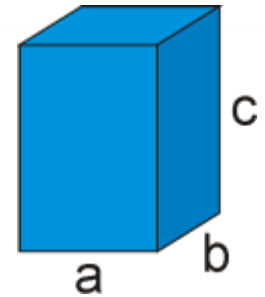
Layer thickness



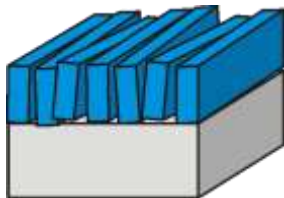
Chemical composition



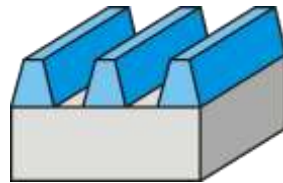
Mismatch & relaxation



Lattice parameters



Defects & Crystal size

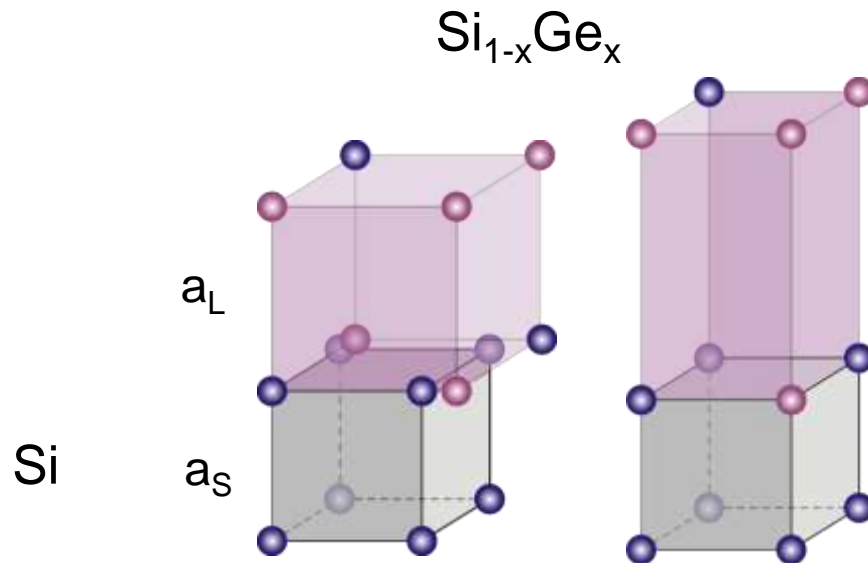


Lateral structure

Pseudomorphic and relaxed strain state



- Relaxed layer lattice mismatch : $\frac{\Delta a}{a_{rel}} = \frac{a_L - a_S}{a_S}$

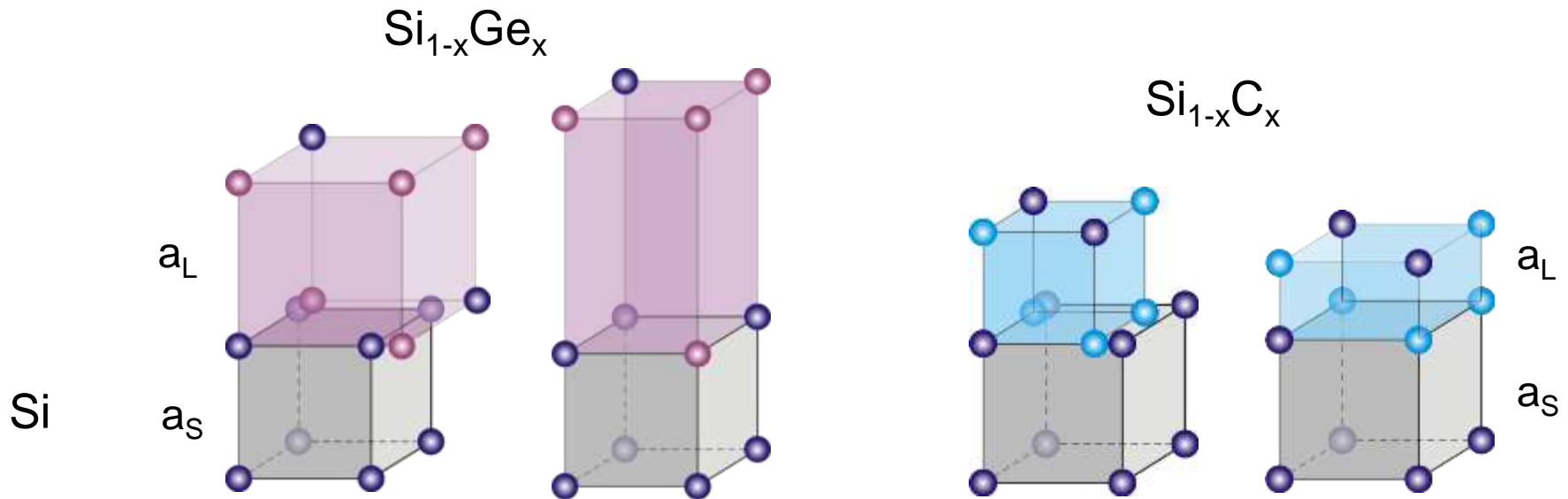


- Compressive strain : $\frac{\Delta a}{a_{rel}} > 0$

Pseudomorphic and relaxed strain state



- Relaxed layer lattice mismatch : $\frac{\Delta a}{a_{rel}} = \frac{a_L - a_S}{a_S}$



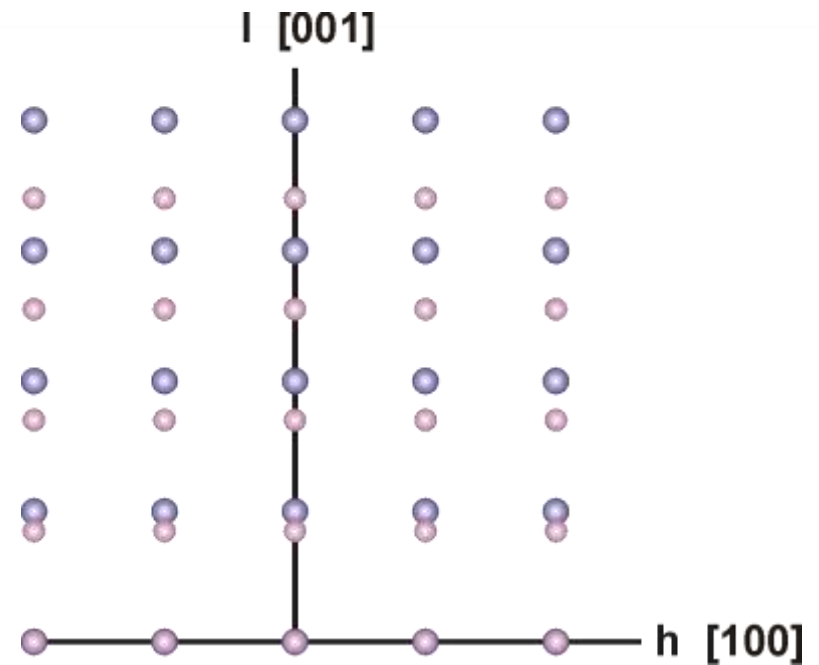
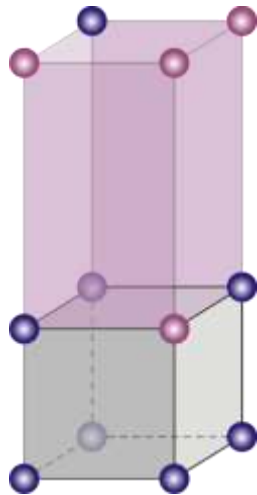
- Compressive strain : $\frac{\Delta a}{a_{rel}} > 0$

- Tensile strain : $\frac{\Delta a}{a_{rel}} < 0$

Epitaxial Layers in Reciprocal Space



Pseudomorphic Layer

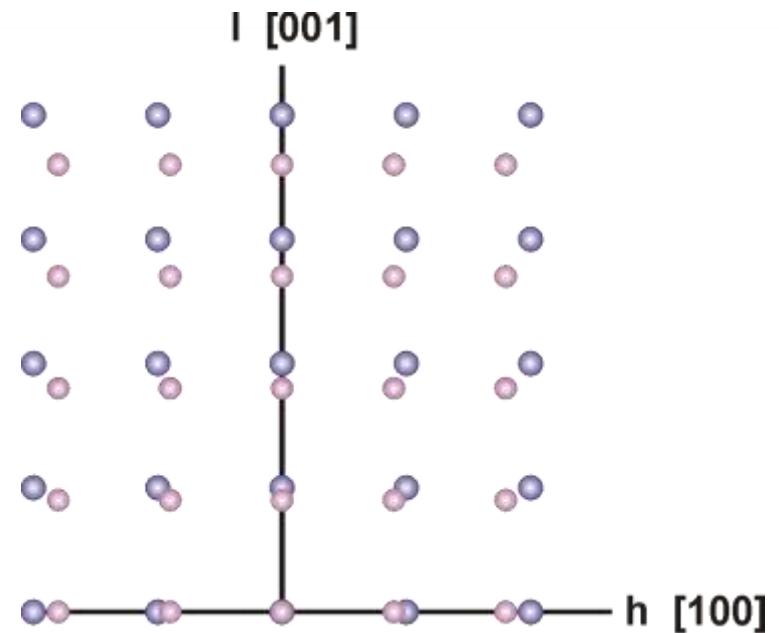
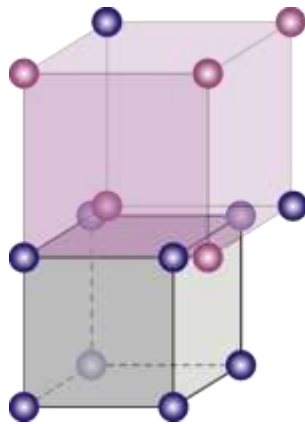


- substrate
- fully strained layer

Epitaxial Layers in Reciprocal Space

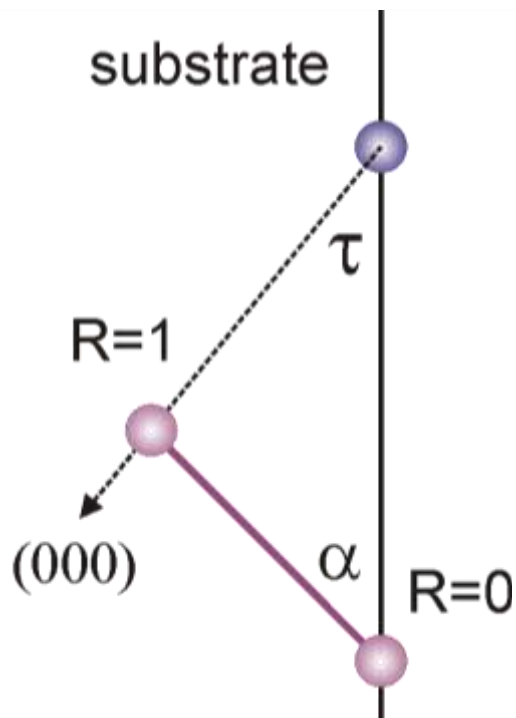


Completely relaxed layer



- substrate
- fully relaxed layer

The relaxation line



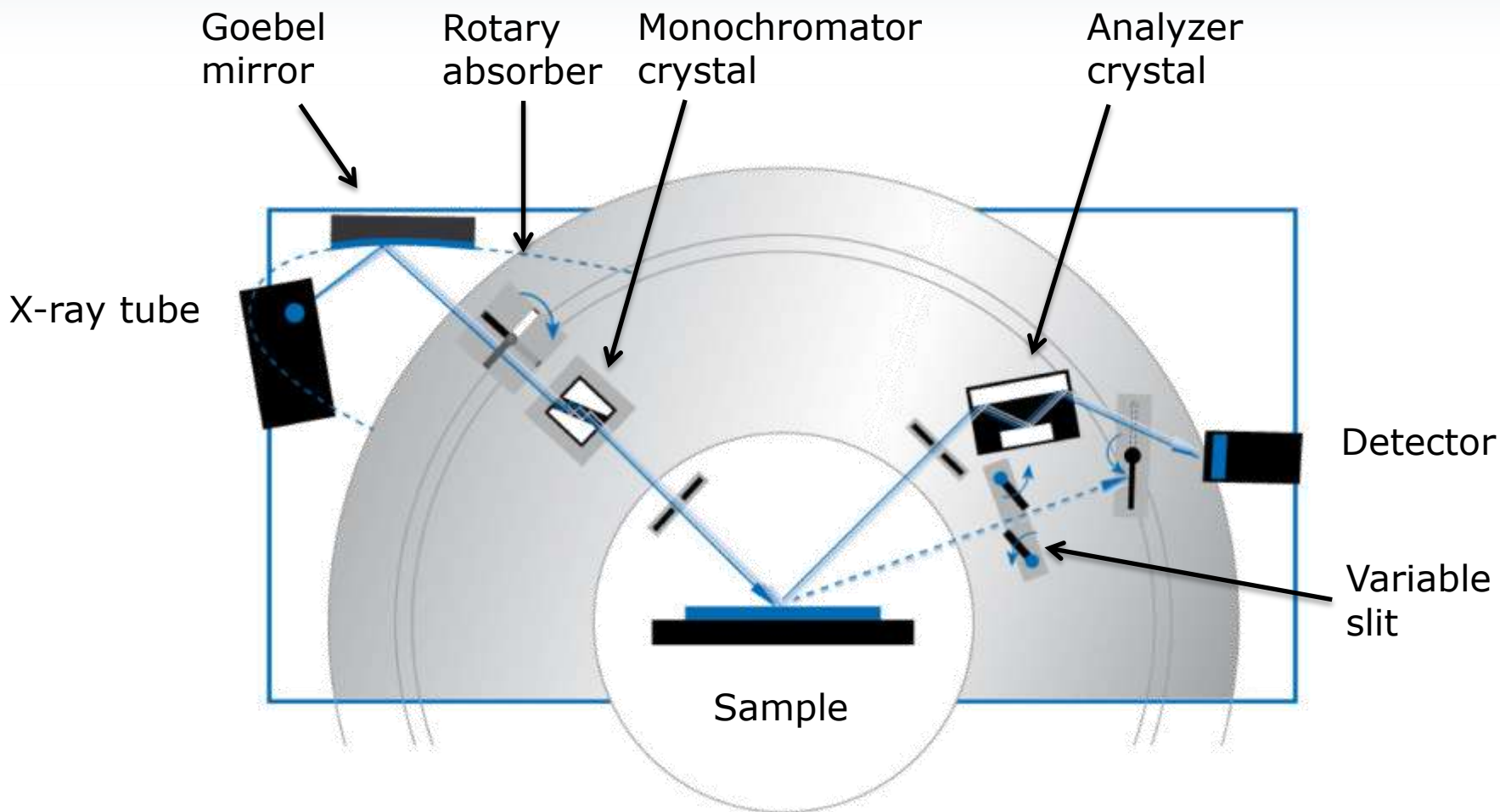
- The reflection of a **fully strained** layer is located on a **perpendicular** line.
- A reflection of a **fully relaxed** layer is on a line through the **substrate reflection** and **(000)**.
- Reflections of **partly relaxed** layers are on **the relaxation line**.

$$\tan \alpha = -\tan \tau / D$$

Theory of elasticity: $D \approx 0.5, \dots, 1$

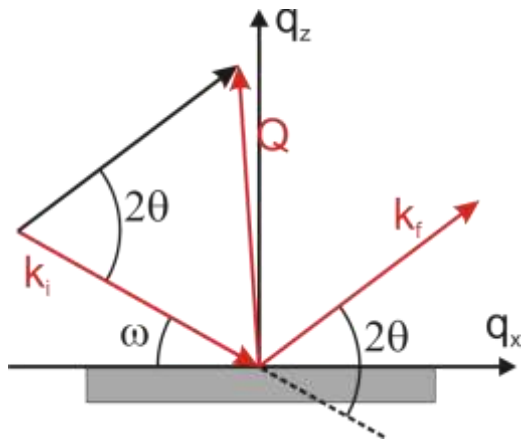
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Diffractometer configuration for measuring RSMs



How to measure RSMs?

Scan Types

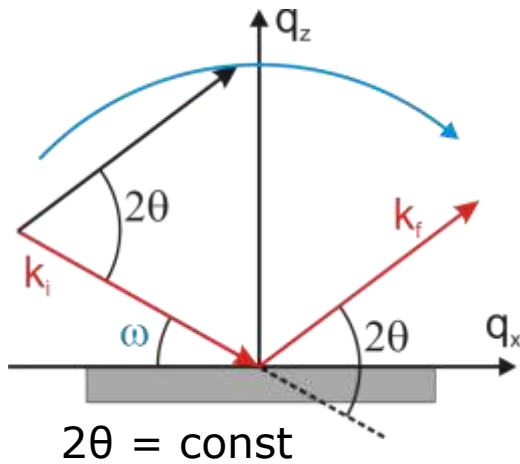


How to measure RSMs?

Scan Types



Rocking curve

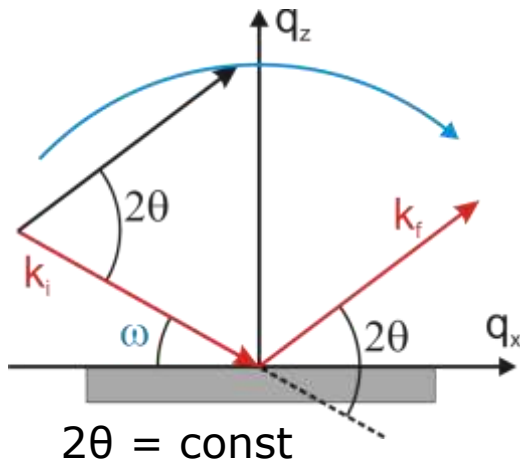


How to measure RSMs?

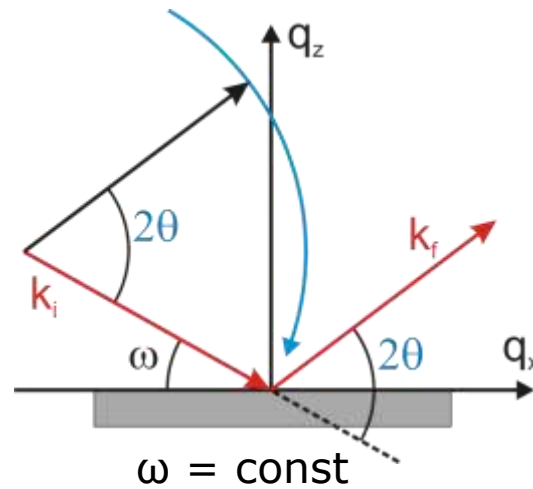
Scan Types



Rocking curve



Detector scan

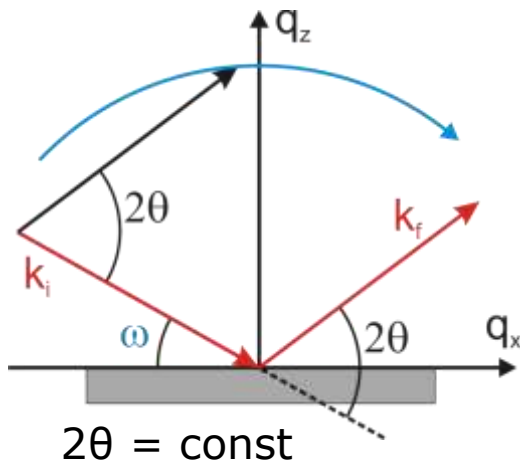


How to measure RSMs?

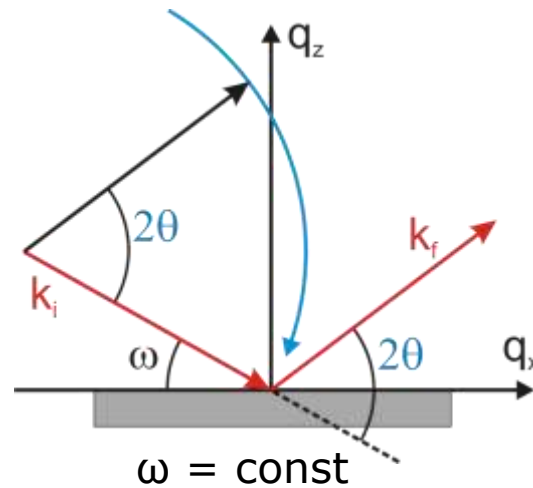
Scan Types



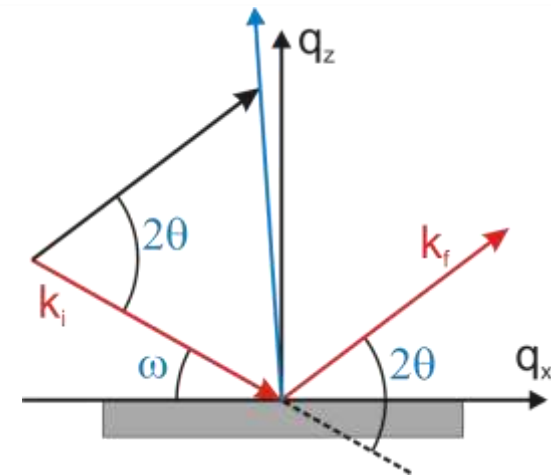
Rocking curve



Detector scan



$2\theta/\omega$, $\omega/2\theta$ scan

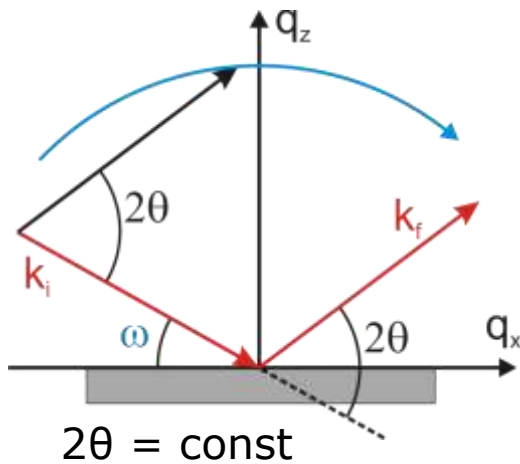


How to measure RSMs?

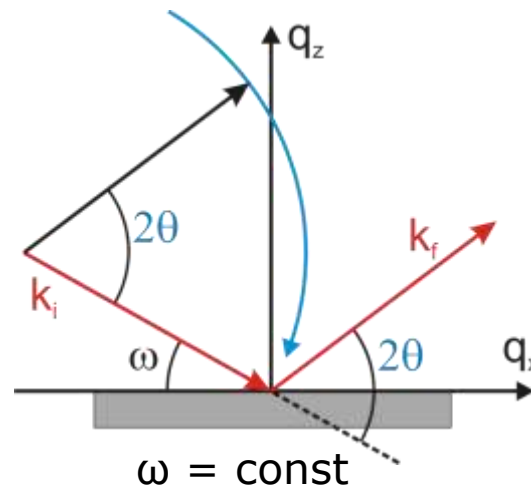
Scan Types



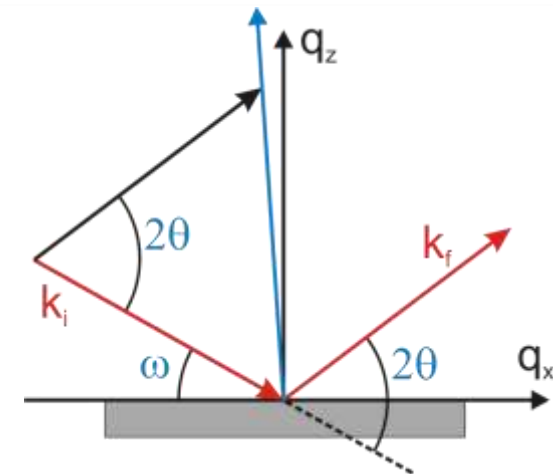
Rocking curve



Detector scan



$2\theta/\omega$, $\omega/2\theta$ scan

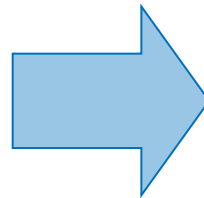
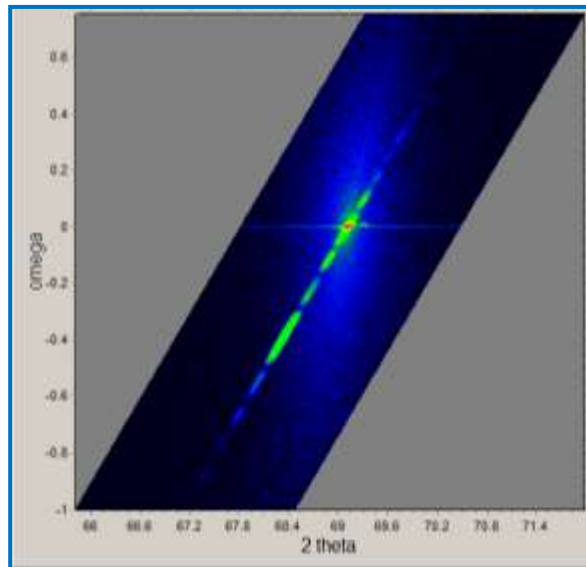


- reciprocal space scans
 - q_x scan, $q_z = \text{const}$
 - q_z scan, $q_x = \text{const}$

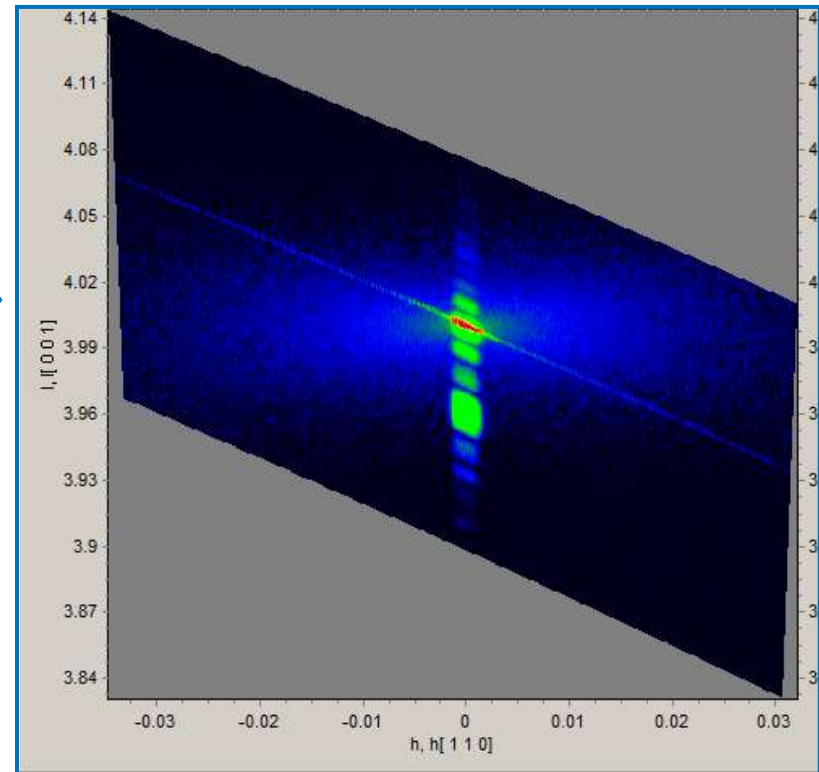
Conversion from angular to reciprocal lattice units



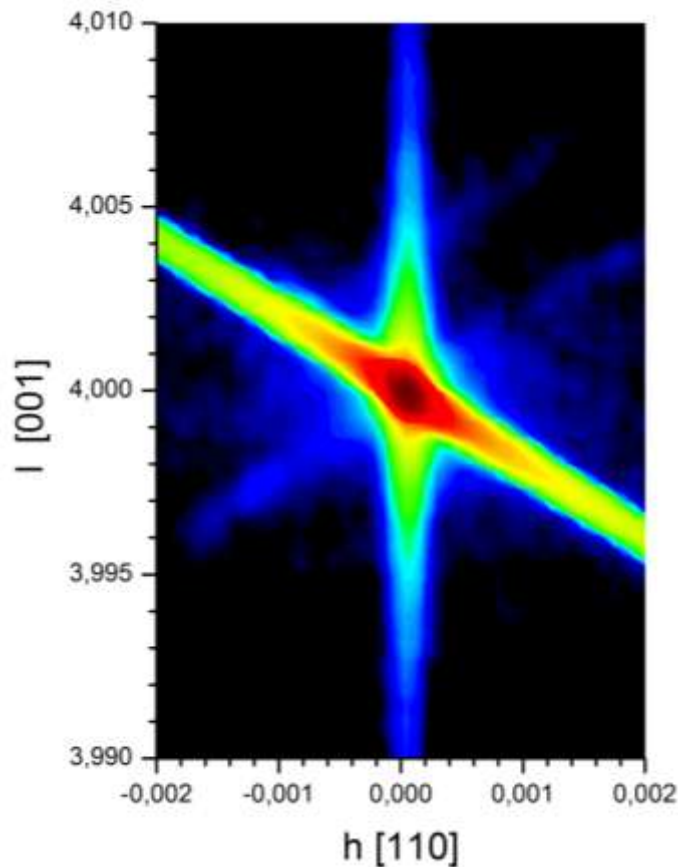
Measurement is performed in angular space



Analyses are done in reciprocal space

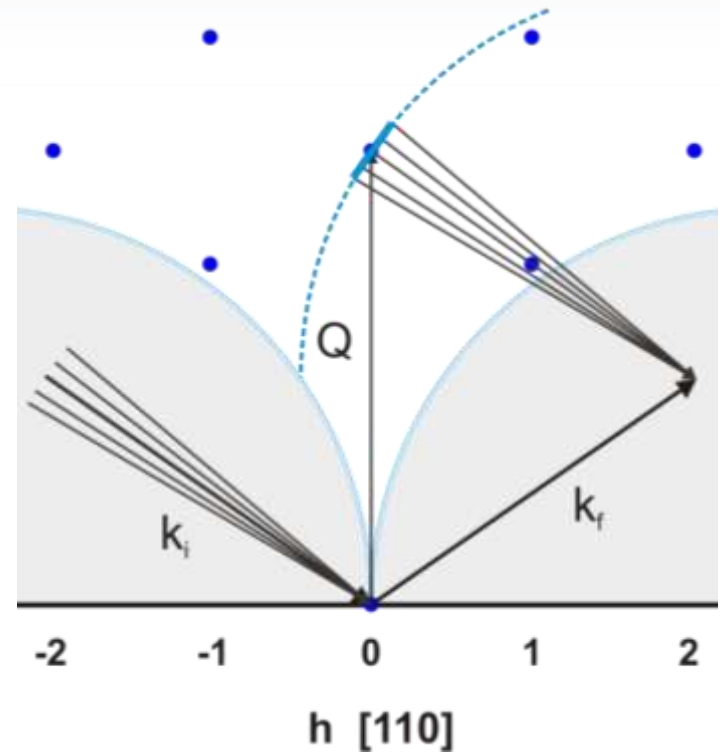
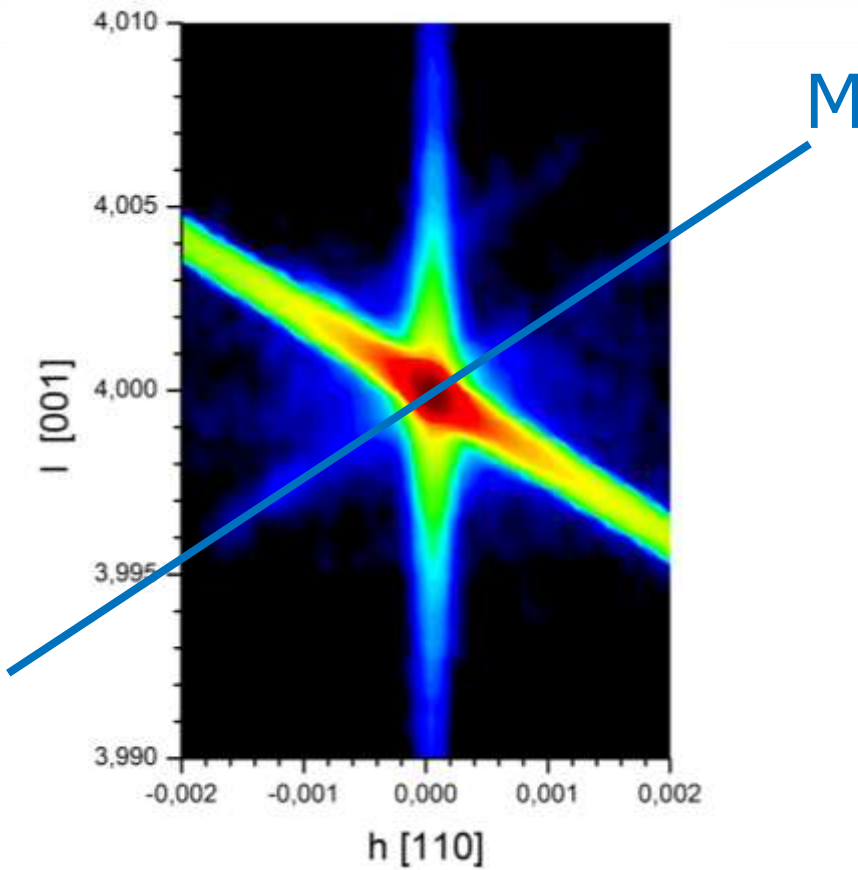


The instrumental resolution function in RSM



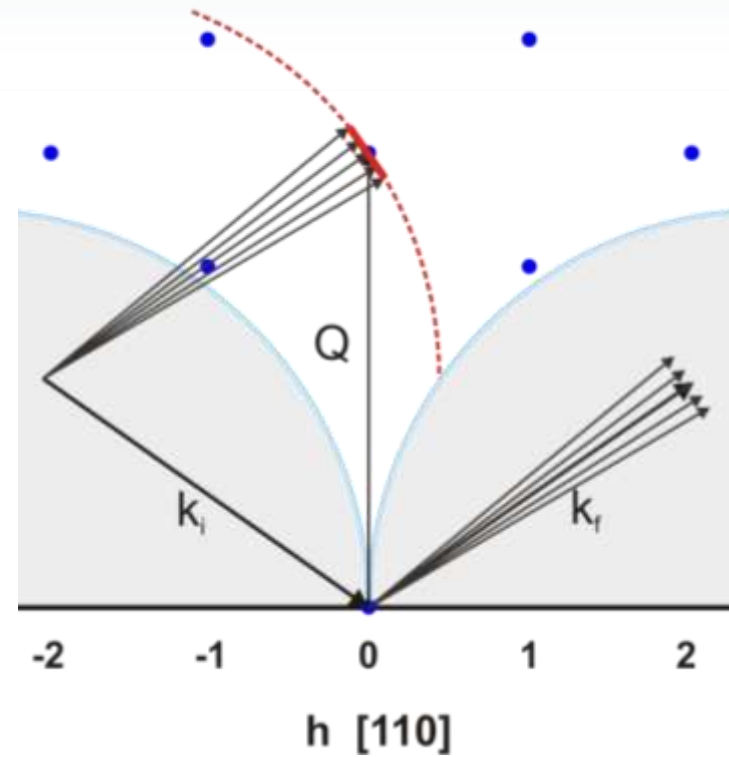
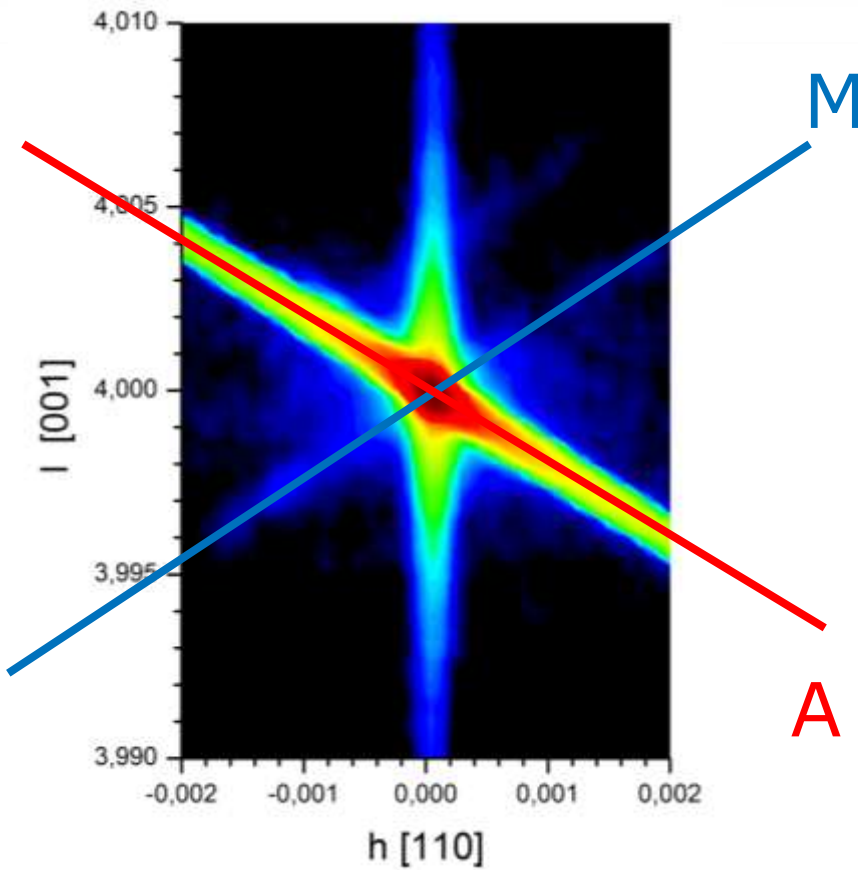
- The recorded intensity at any point in reciprocal space is an average over the respective resolution element.
- Example : Si(004) reflection measured with
 - 2xGe(004a) monochromator
 - 1xGe(002) analyzer

The instrumental resolution function in RSM



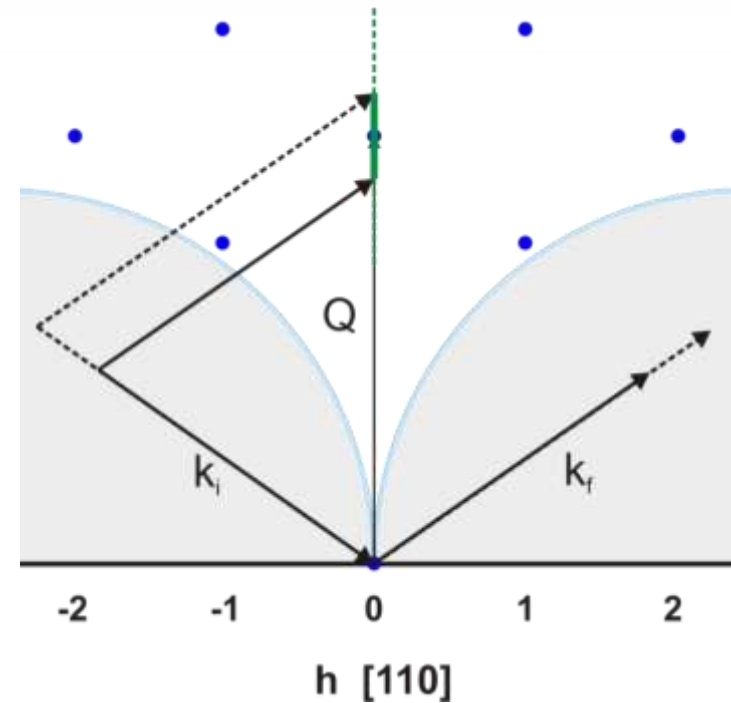
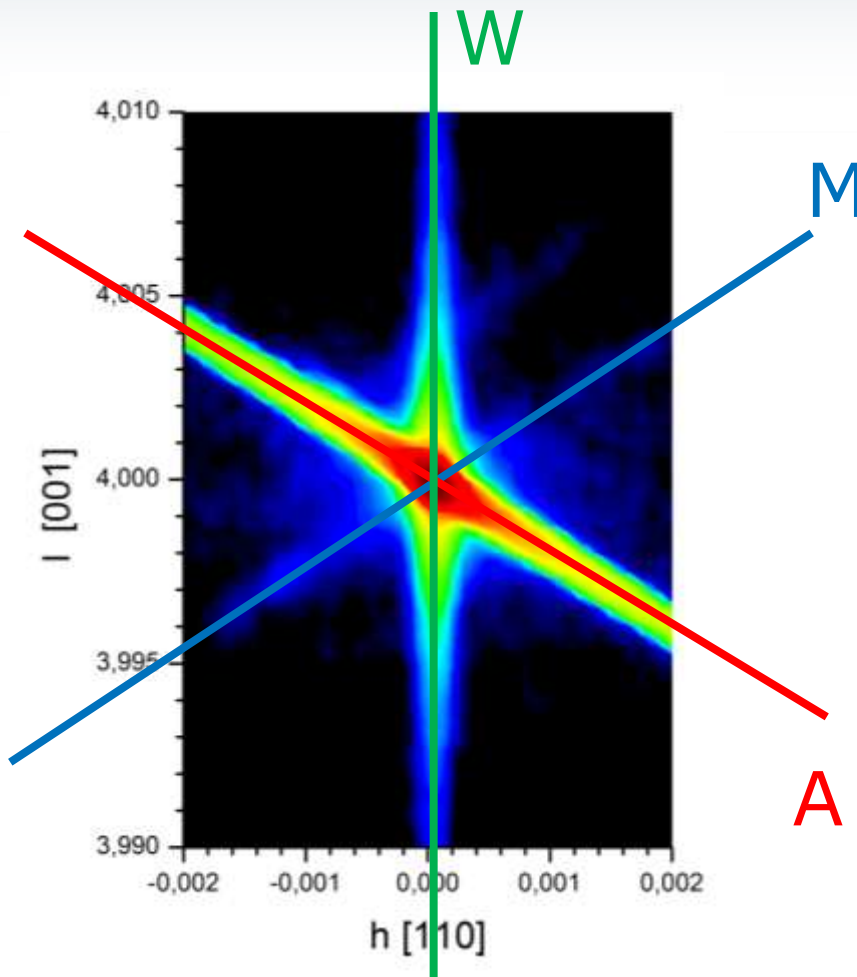
Monochromator streak is normal to incident beam

The instrumental resolution function in RSM



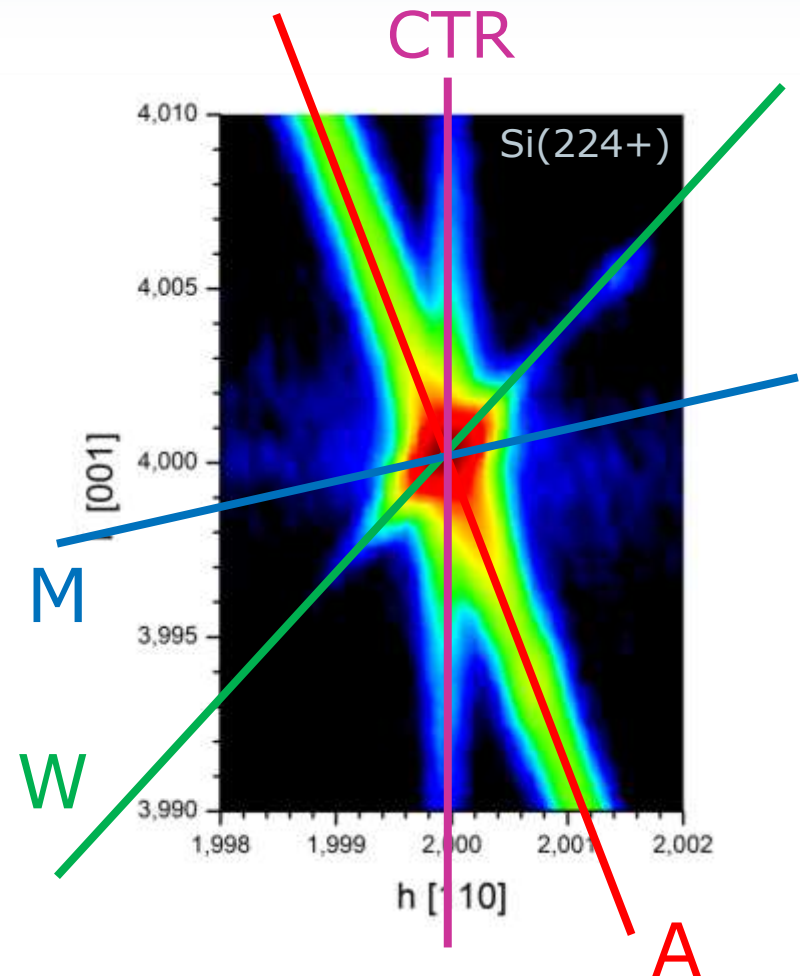
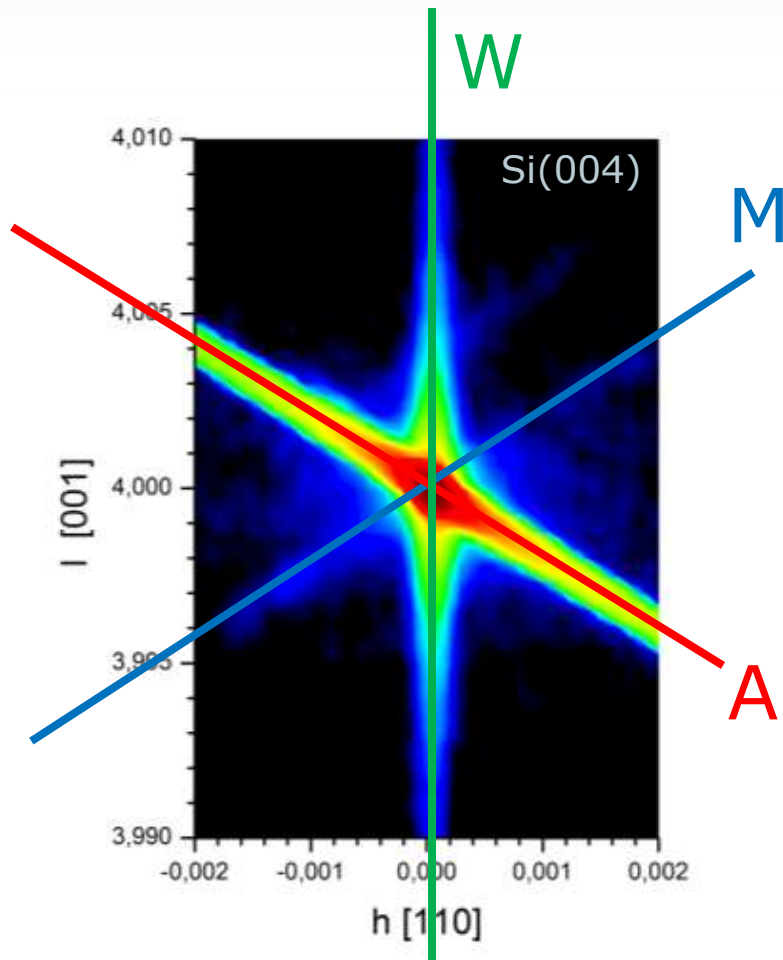
Analyzer streak is normal to exit beam

The instrumental resolution function in RSM



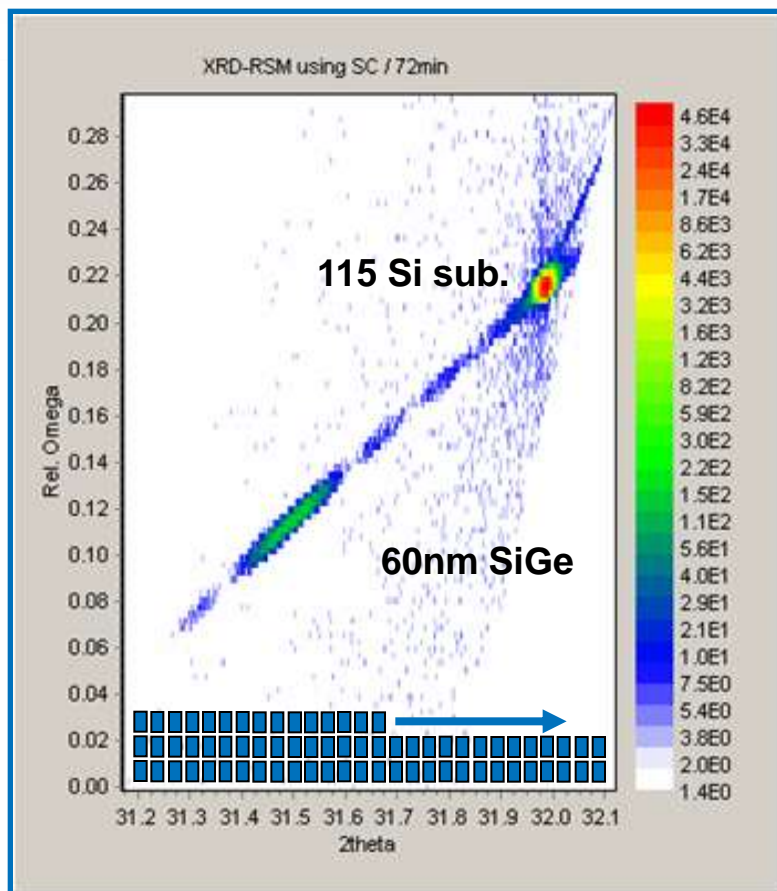
wavelength streak is along a line through (000)

The instrumental resolution function in RSM

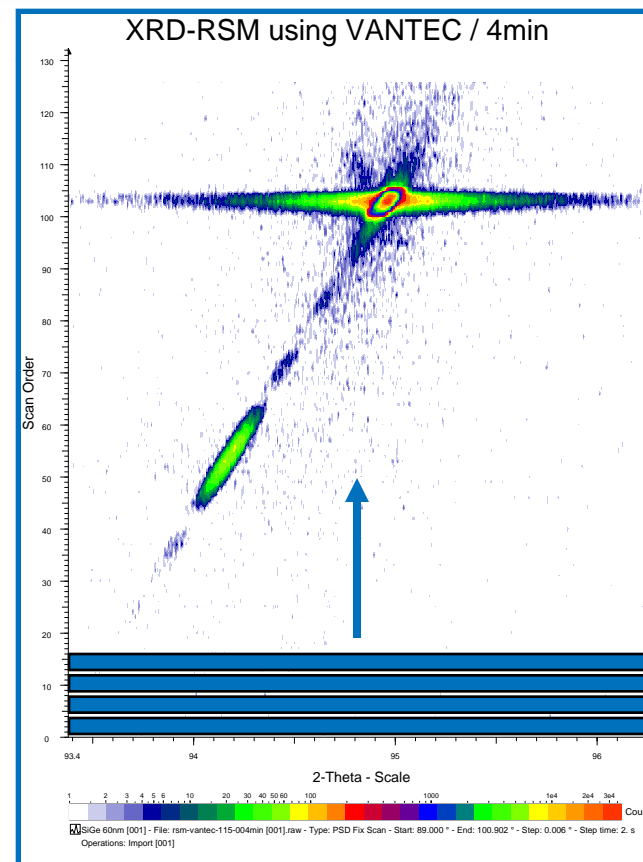


- What is Reciprocal Space
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 - **Technique**
 - Examples
- RSMs with 2D-detectors

Reciprocal Space Maps Measurement with 1D detectors Scintillation Counter vs. VÅNTEC-1



Scintillation Counter: 72 min



VÅNTEC-1: 4 min

1D-detectors for fast RSM measurements: LYNXEYE



- Silicon strip detector
- 192 strips of 75 μm width
- Total window width 14.4 mm
- Resolution at 300 mm $\approx 0.012^\circ$
- Subsampling in Fast-scan mode
- Can be used as a 0D-detector

1D-detectors for fast RSM measurements: LYNXEYE and VANTEC-1



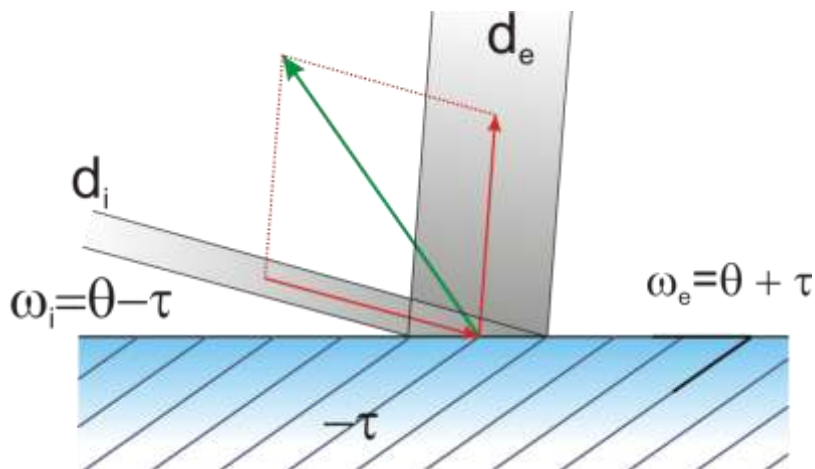
- Silicon strip detector
- Total window width 14.4mm
- 192 strips of 75 μ m width.
- Resolution at 300mm \approx 0.012 $^\circ$
- Subsampling in Fast-scan mode
- Can be used as a 0D-detector

- Gas detector (Xe-CO₂)
- 50x16 mm² active area, simultaneous up to 12 $^\circ$ in 2θ
- 1600 electronic channels
- Resolution at 300 mm \approx 0.006 $^\circ$
- Low detector noise

Influence of the measurement geometry on the resolution



Grazing incidence geometry



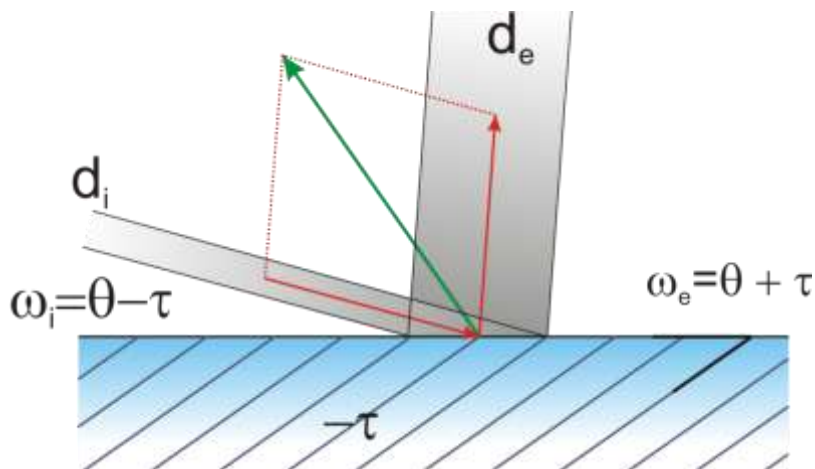
- Asymmetry factor $b = \frac{\sin(\omega_i)}{\sin(\omega_e)}$

- Exit beam width $d_e = \frac{d_i}{b}$

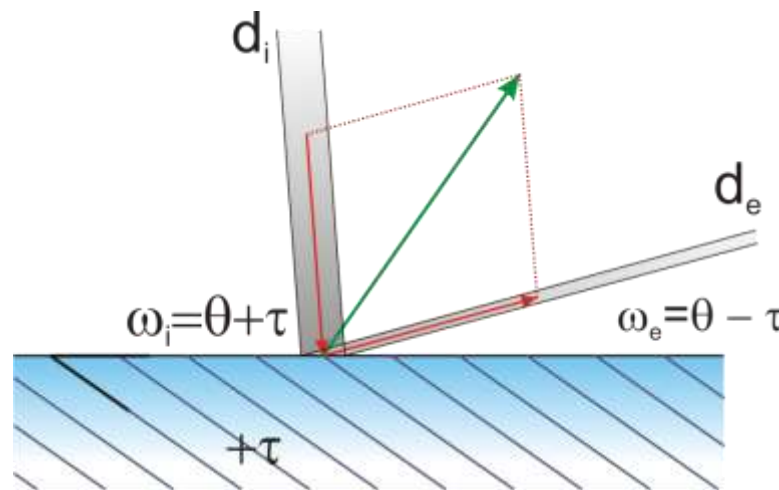
Influence of the measurement geometry on the resolution



Grazing incidence geometry



Grazing exit geometry



- Asymmetry factor $b = \frac{\sin(\omega_i)}{\sin(\omega_e)}$

- Exit beam width $d_e = \frac{d_i}{b}$

Influence of the measurement geometry on the resolution (2)



- When using a 1D-detector for the RSM, the reflection should be chosen such that the **beam compression is high**.
- The **incident beam** should be adapted to achieve the **highest possible resolution**.

hkl	ω_i	ω_e	b	d_{inc} (75 μm)
113+	56.2°	2.9°	15.9	1.1 mm
224+	79.2°	8.8°	6.42	0.5 mm
115+	63.3°	32.7°	1.7	0.1 mm

Si reflections for Cu-K α radiation

- When RSMs are measured using an **analyzer crystal**, the full incident beam can be used and **the geometry is not critical**.

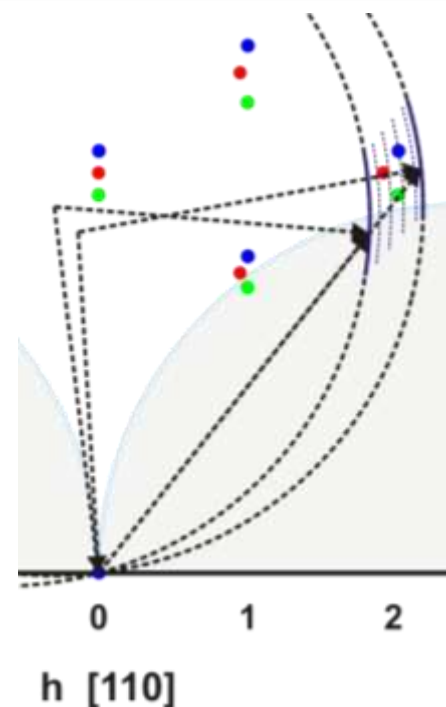
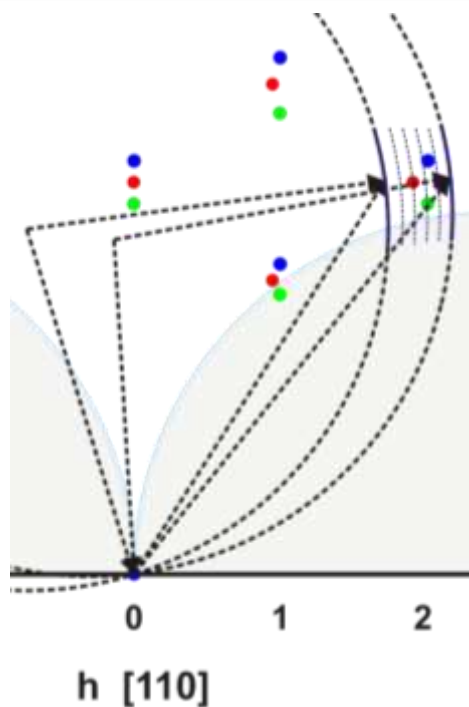
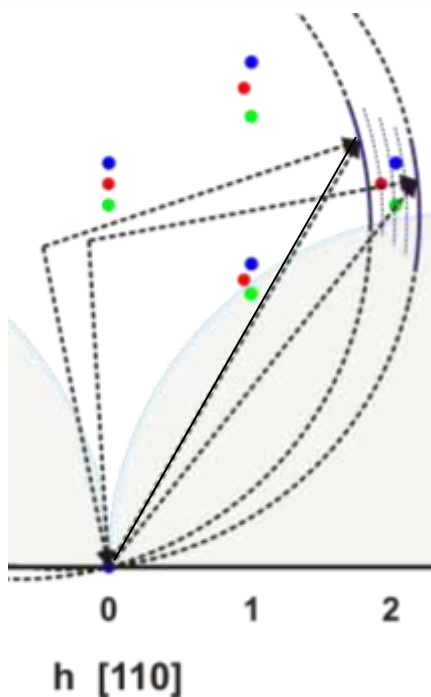
RSMs with a 1D detector: Choice of the loop scan



Looped over rocking curve

Looped over h-scan

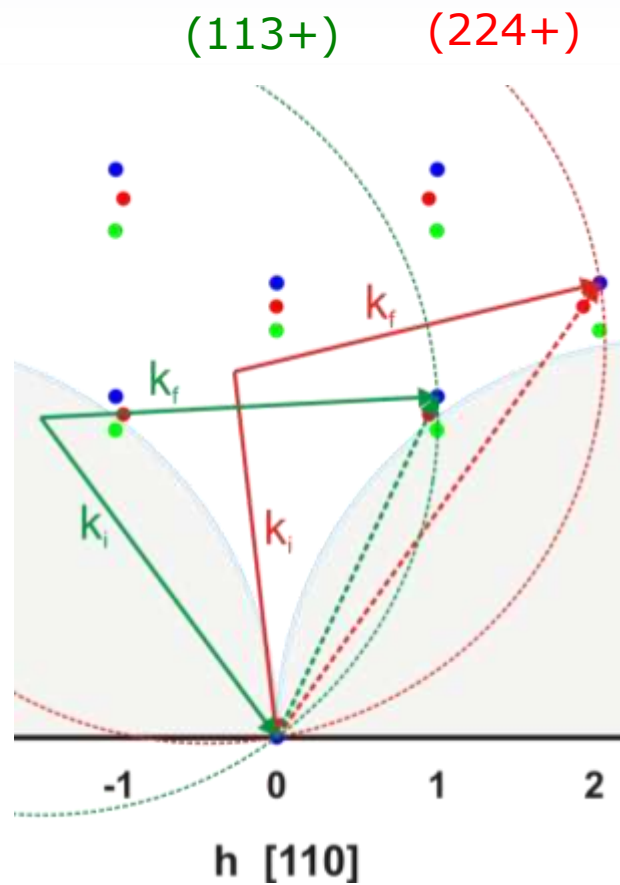
Looped over $2\theta/\omega$ scan



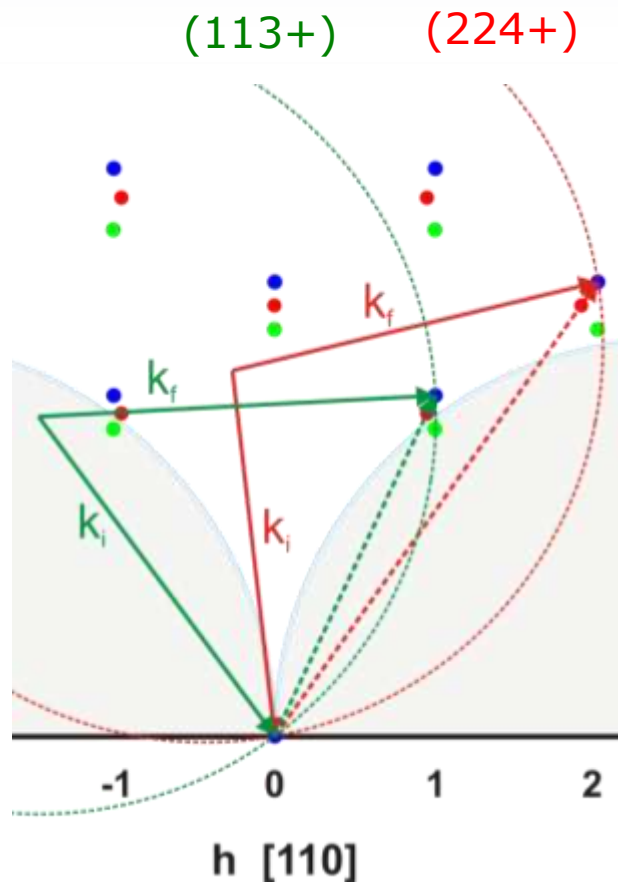
Pseudomorphic layers

Fully relaxed layers

Choosing the appropriate reflection for the RSM: (113+) vs. (224+)



Choosing the appropriate reflection for the RSM: (113+) vs. (224+)



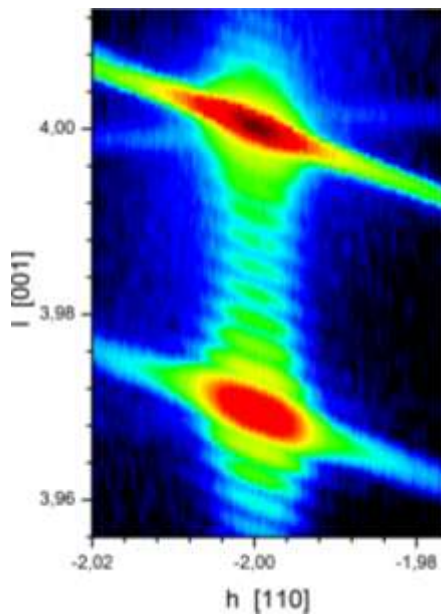
- + Structures are more compact. **Faster RSM.**
- + Higher structure factor. **More intensity.**
- + Detector Snapshot is almost like a I-scan. **Faster RSM.**
- + Beam Compression factor is higher. **Better resolution.**
- **Penetration depth** decreases at grazing angles. Deeper layers of the sample may not show up.
- **Less precision** in lattice parameter determination.

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RSMs from $\text{In}_{0.06}\text{Ga}_{0.96}\text{As}$ films on GaAs with different layer thicknesses



$d = 200 \text{ nm}$

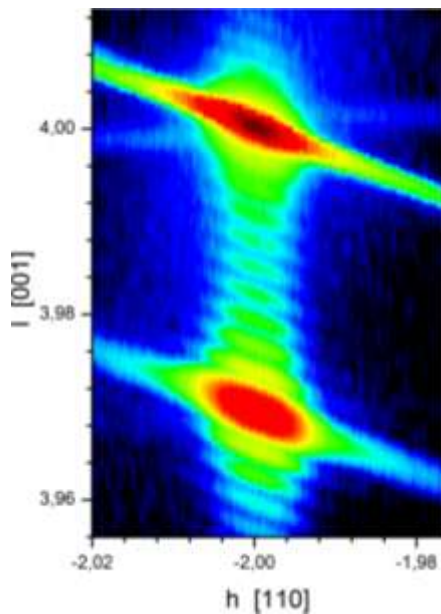


Samples provided by F. Rinaldi (Uni Ulm / Bruker AXS)

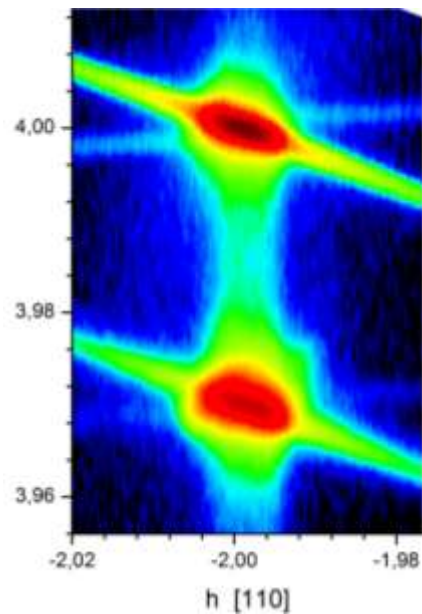
RSMs from $\text{In}_{0.06}\text{Ga}_{0.96}\text{As}$ films on GaAs with different layer thicknesses



d = 200 nm



d = 400 nm

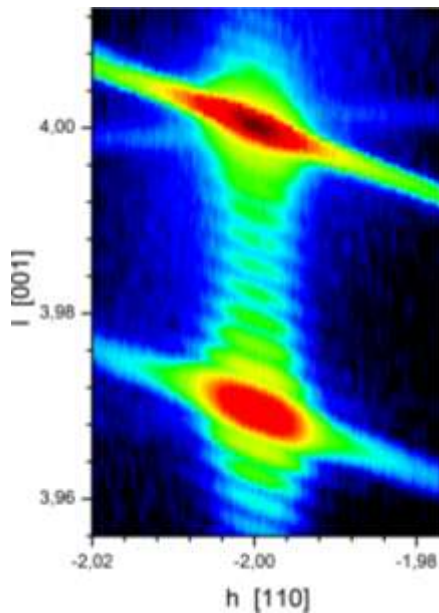


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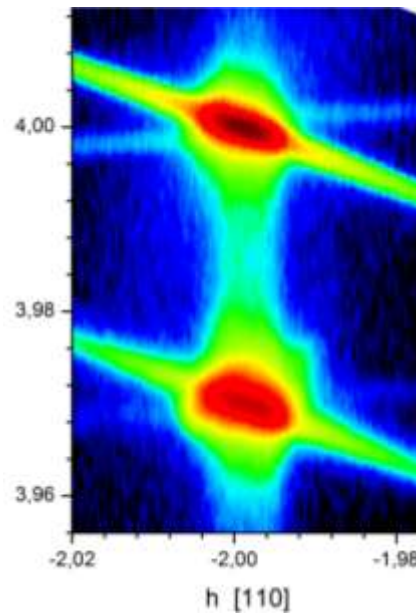
RSMs from $\text{In}_{0.06}\text{Ga}_{0.96}\text{As}$ films on GaAs with different layer thicknesses



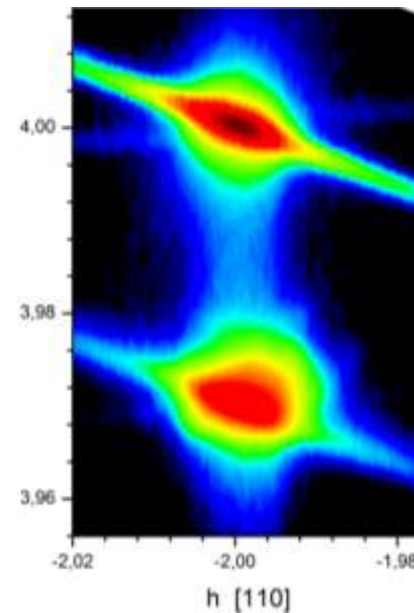
$d = 200 \text{ nm}$



$d = 400 \text{ nm}$



$d = 450 \text{ nm}$

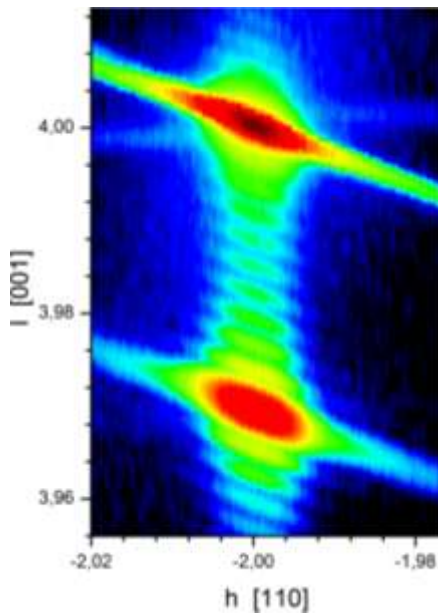


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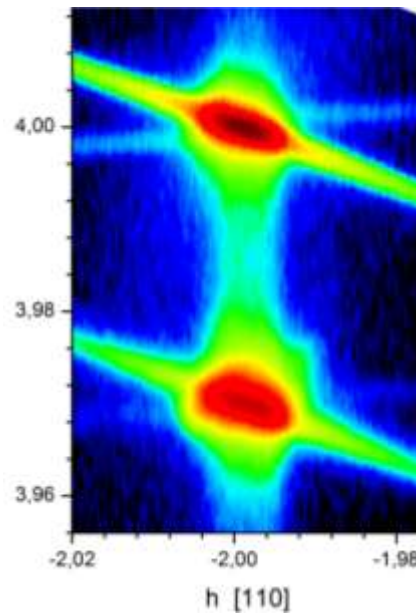
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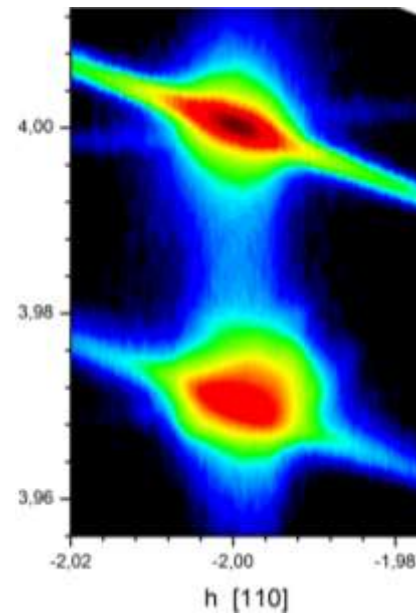
$d = 200 \text{ nm}$



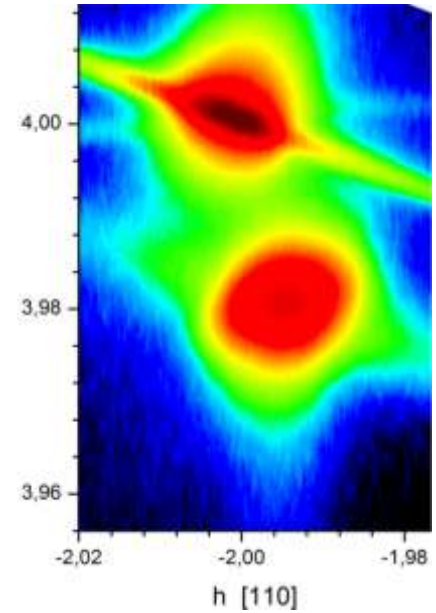
$d = 400 \text{ nm}$



$d = 450 \text{ nm}$

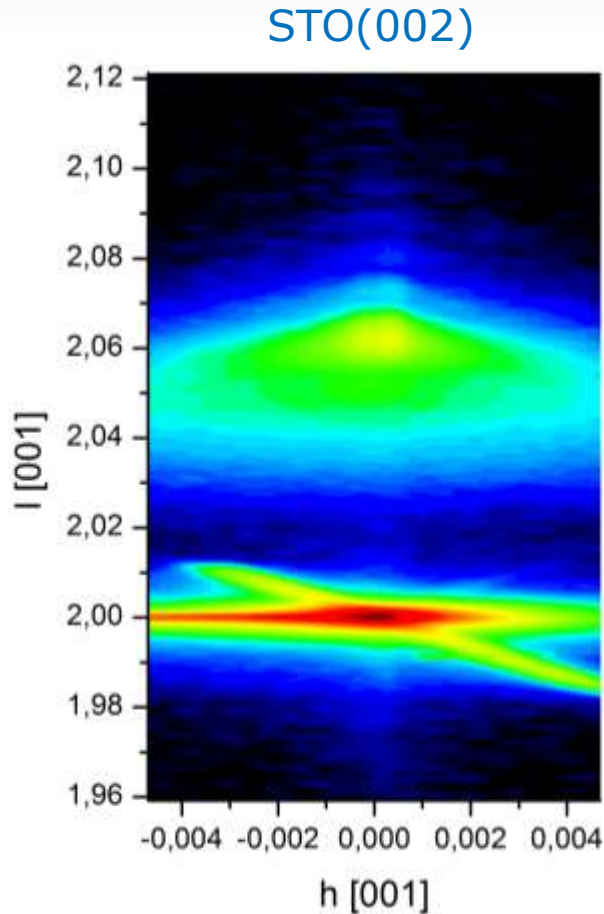


$d = 800 \text{ nm}$



Samples provided by F. Rinaldi (Uni Ulm / Bruker AXS)

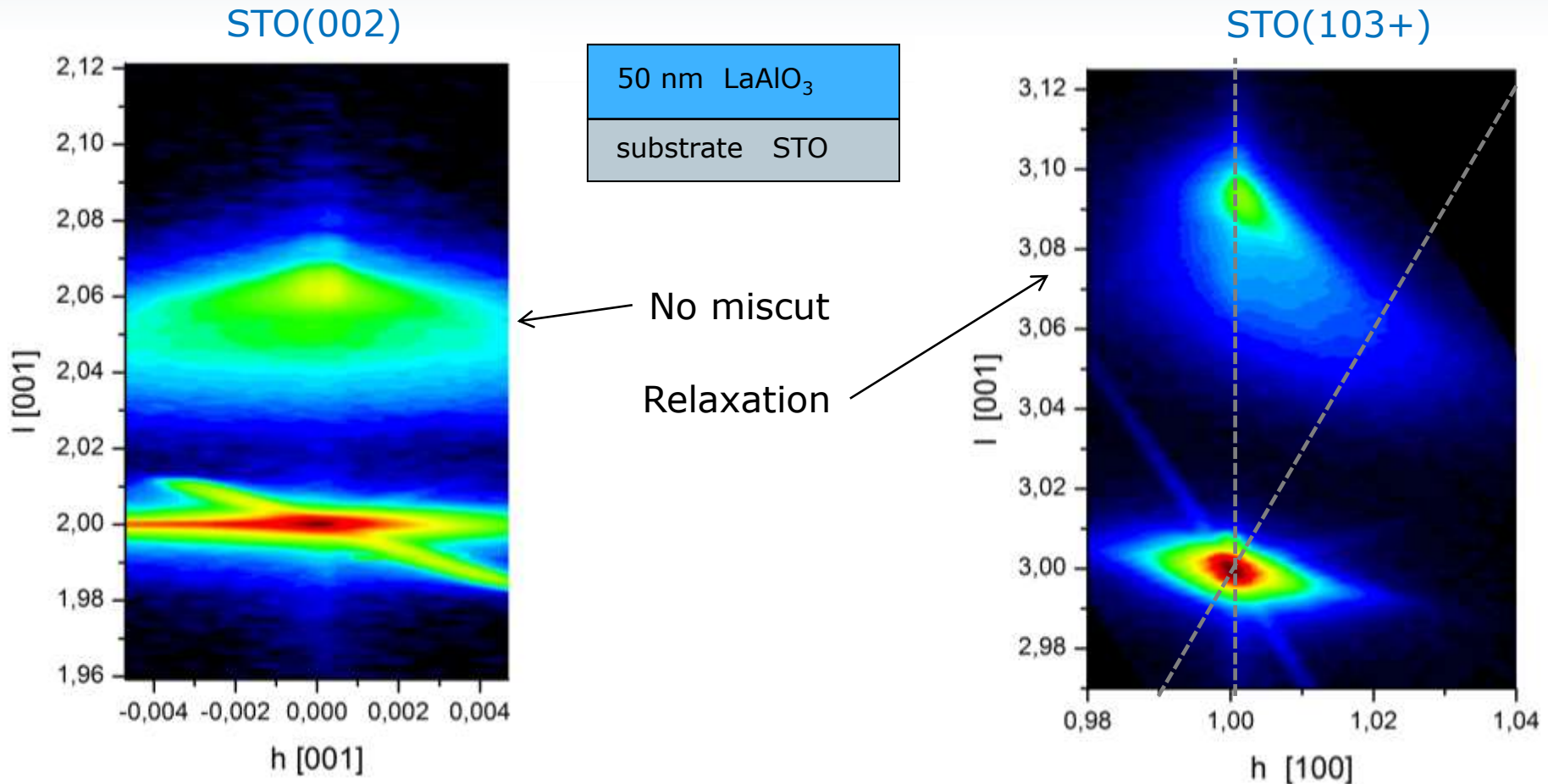
Example: LaAlO_3 on STO



50 nm LaAlO_3
substrate STO

Sample courtesy of Dirk Fuchs (Institute of solid state physics, KIT)

Example: LaAlO_3 on STO



Sample courtesy of Dirk Fuchs (Institute of solid state physics, KIT)

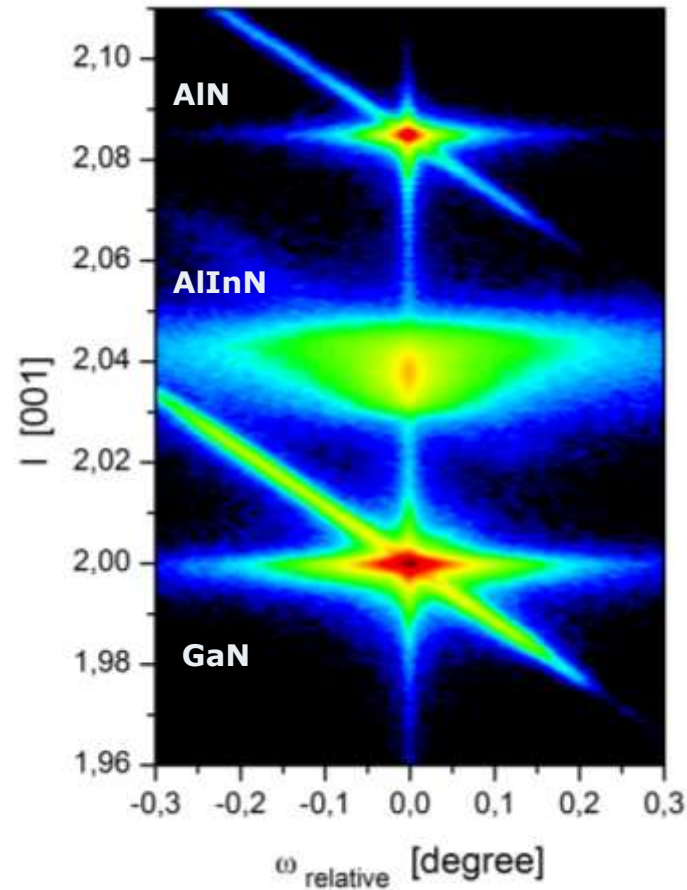
Example: GaN-based HEMT structure



GaN(002)

200 nm $\text{Al}_{0.85}\text{In}_{0.15}\text{N}$
1 nm AlN
1000 nm GaN
350 nm AlN
substrate Al_2O_3

Sample courtesy of L. R. Khoshroo (RWTH Aachen)



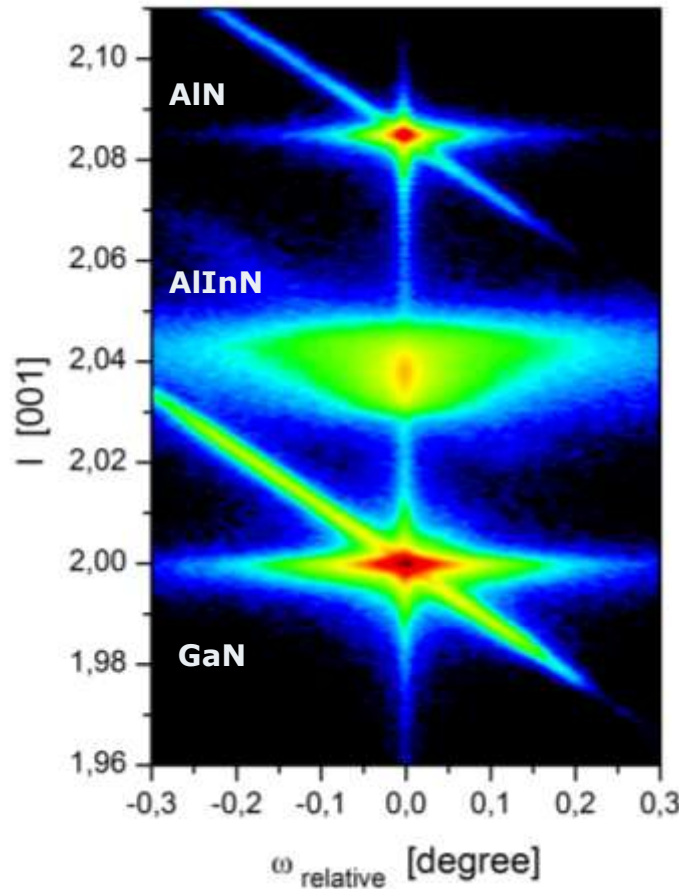
Example: GaN-based HEMT structure



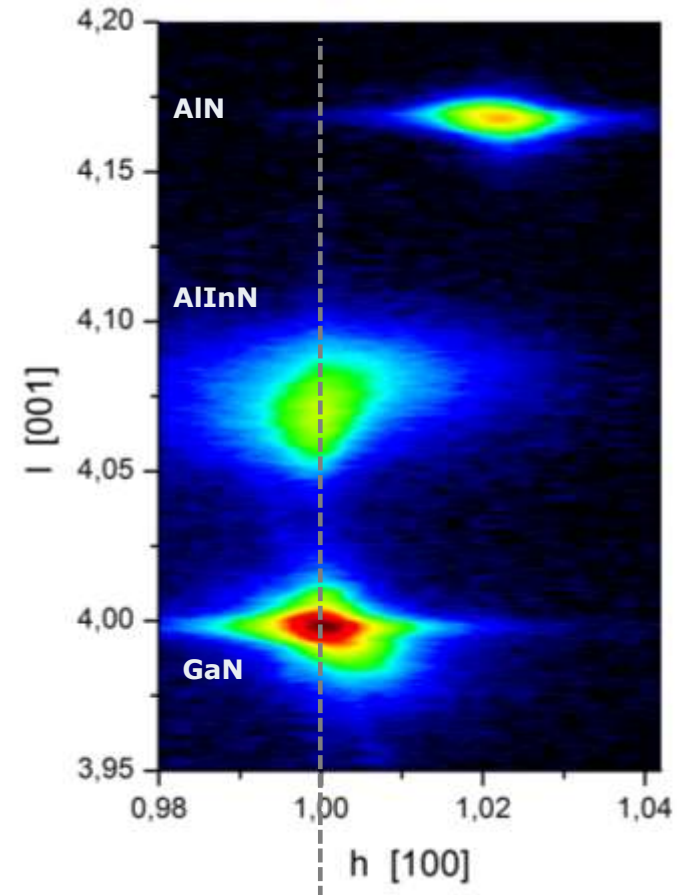
200 nm $\text{Al}_{0.85}\text{In}_{0.15}\text{N}$
1 nm AlN
1000 nm GaN
350 nm AlN
substrate Al_2O_3

Sample courtesy of L. R. Khoshroo (RWTH Aachen)

GaN(002)

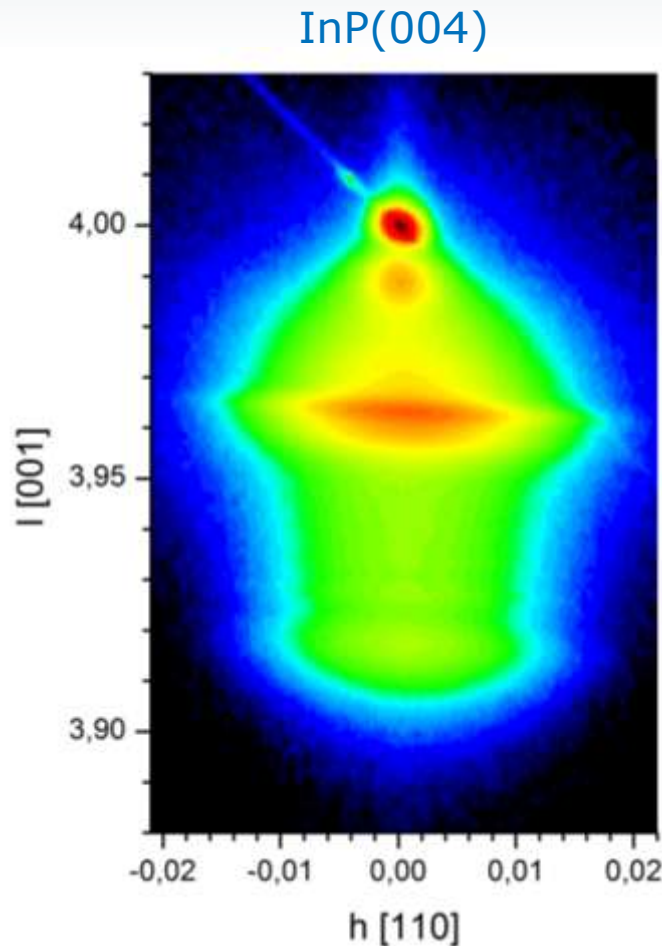


GaN(104+)



Example: HEMT structure with graded buffer layers

10 nm	$\text{In}_{0.65}\text{Ga}_{0.35}\text{As}$
120 nm	$\text{In}_{0.65}\text{Al}_{0.35}\text{As}$
30 nm	$\text{In}_{0.65}\text{Ga}_{0.35}\text{As}$
50 nm	$\text{In}_{0.65}\text{Al}_{0.35}\text{As}$
200 nm	$x=0.75$
$\text{In}_x\text{Al}_{1-x}\text{As}$	$x=0.65$
500 nm	$x=0.65$
$\text{In}_x\text{Al}_{1-x}\text{As}$	$x=0.52$
50 nm	$\text{In}_{0.52}\text{Al}_{0.48}\text{As}$
substrate	InP



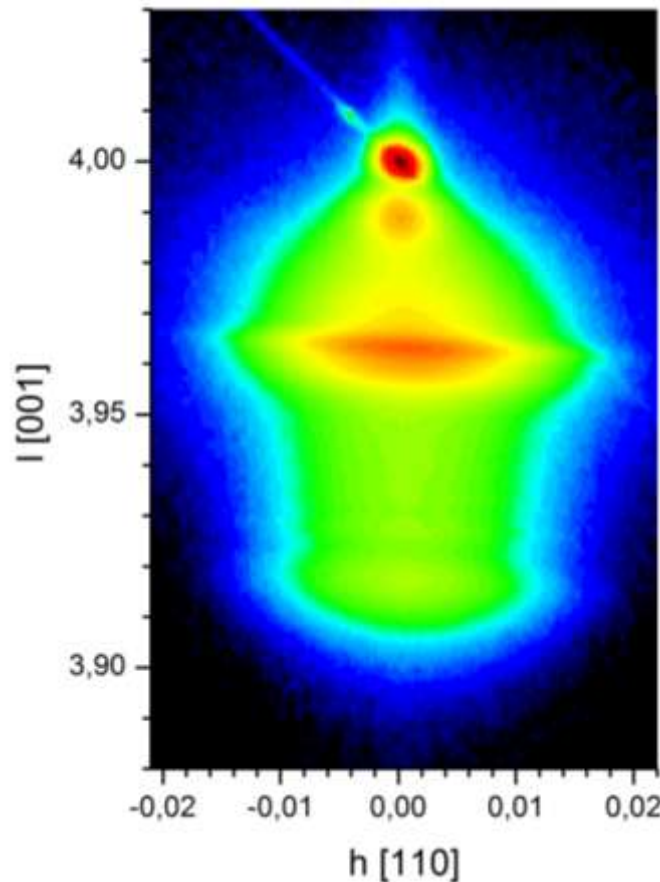
Sample courtesy of Ian Farrer (University of Cambridge)

Example: HEMT structure with graded buffer layers

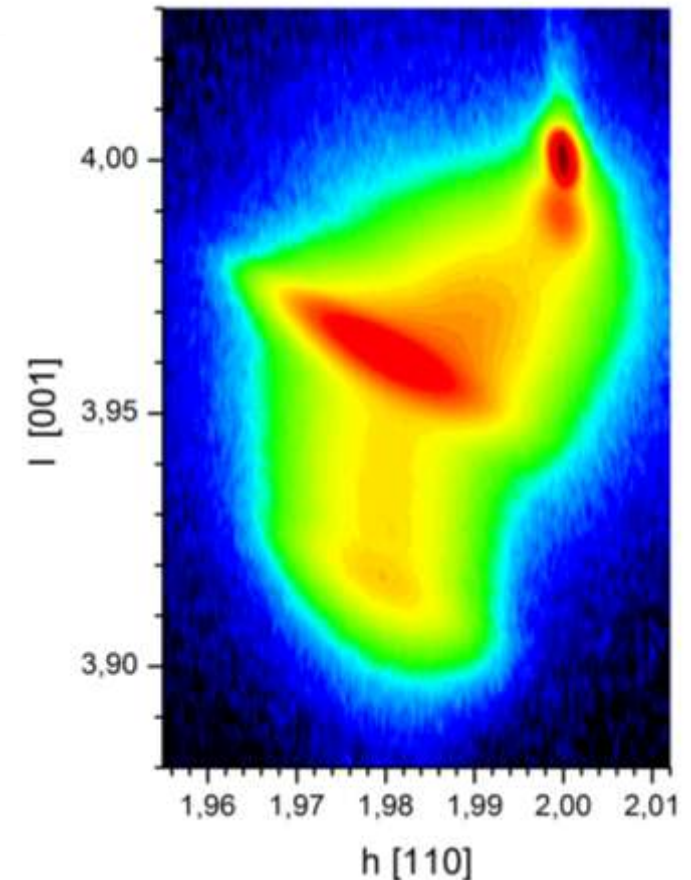


10 nm	$\text{In}_{0.65}\text{Ga}_{0.35}\text{As}$
120 nm	$\text{In}_{0.65}\text{Al}_{0.35}\text{As}$
30 nm	$\text{In}_{0.65}\text{Ga}_{0.35}\text{As}$
50 nm	$\text{In}_{0.65}\text{Al}_{0.35}\text{As}$
200 nm	$\text{In}_x\text{Al}_{1-x}\text{As}$ $x=0.75$
	$x=0.65$
500 nm	$\text{In}_x\text{Al}_{1-x}\text{As}$ $x=0.65$
	$x=0.52$
50 nm	$\text{In}_{0.52}\text{Al}_{0.48}\text{As}$
substrate	InP

InP(004)



InP(224+)

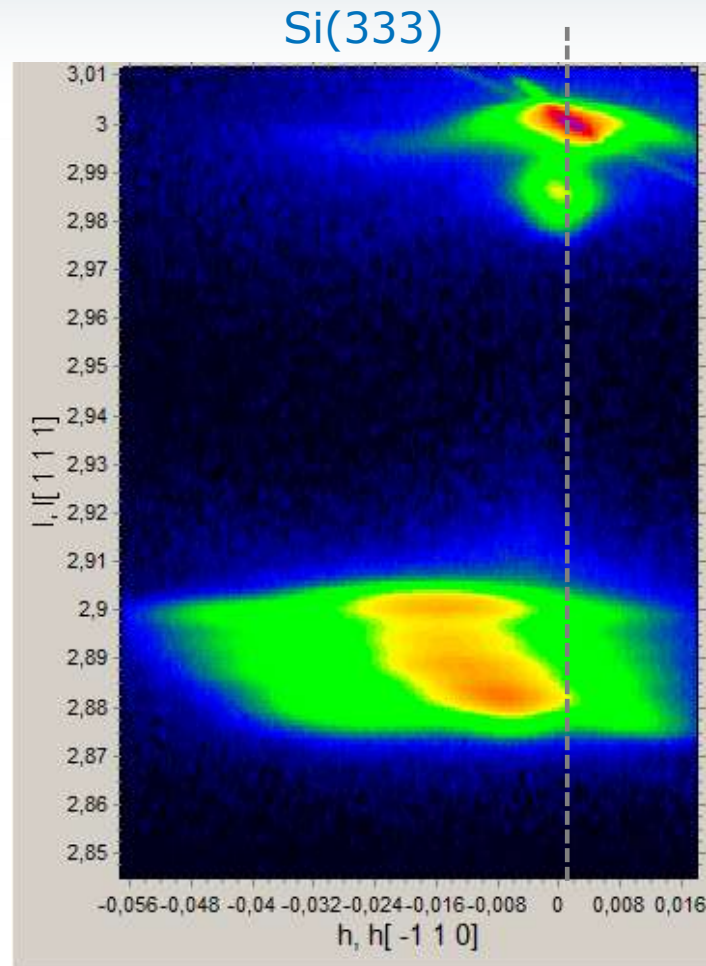


Sample courtesy of Ian Farrer (University of Cambridge)

RSM from a SiGe graded heterostructure: Miscut, Relaxation and Concentration



500 nm $\text{Si}_x\text{Ge}_{1-x}$ $x=20\%$
250 nm $\text{Si}_x\text{Ge}_{1-x}$ $x=15-20\%$
250 nm $\text{Si}_x\text{Ge}_{1-x}$ $x=15\%$
250 nm $\text{Si}_x\text{Ge}_{1-x}$ $x=10-15\%$
250 nm $\text{Si}_x\text{Ge}_{1-x}$ $x=10\%$
250 nm $\text{Si}_x\text{Ge}_{1-x}$ $x=5-10\%$
250 nm $\text{Si}_x\text{Ge}_{1-x}$ $x=5\%$
250 nm $\text{Si}_x\text{Ge}_{1-x}$ $x=0-5\%$
600 nm Ge
substrate Si(111)

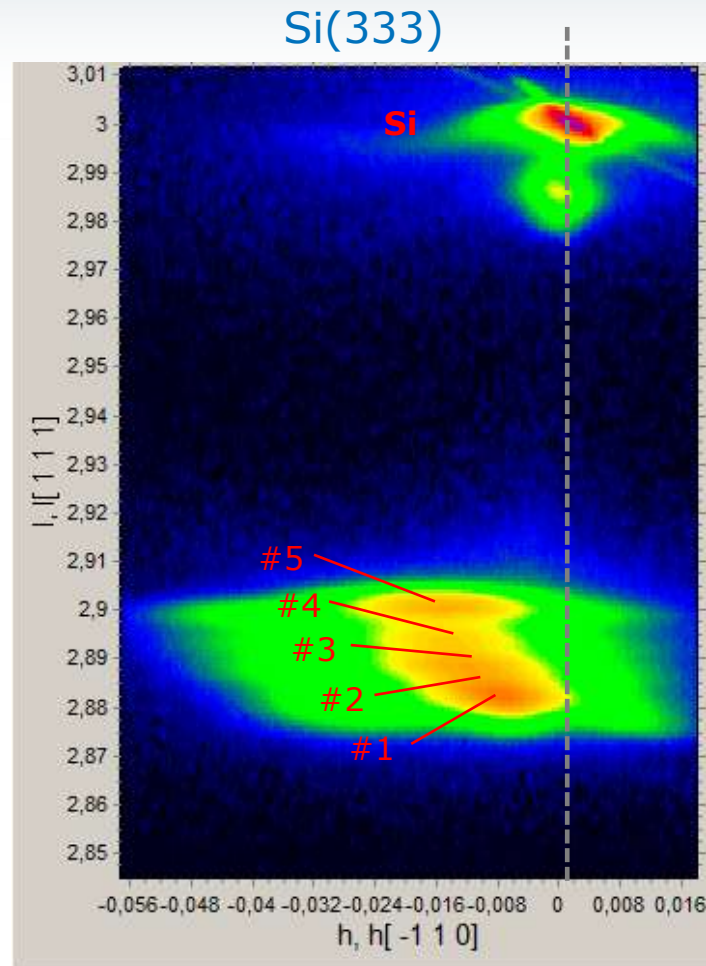


Extract **miscut**
for each SiGe layer

RSM from a SiGe graded heterostructure: Miscut, Relaxation and Concentration



500 nm $\text{Si}_x\text{Ge}_{1-x}$ $x=20\%$	#5
250 nm $\text{Si}_x\text{Ge}_{1-x}$ $x=15-20\%$	
250 nm $\text{Si}_x\text{Ge}_{1-x}$ $x=15\%$	#4
250 nm $\text{Si}_x\text{Ge}_{1-x}$ $x=10-15\%$	
250 nm $\text{Si}_x\text{Ge}_{1-x}$ $x=10\%$	#3
250 nm $\text{Si}_x\text{Ge}_{1-x}$ $x=5-10\%$	
250 nm $\text{Si}_x\text{Ge}_{1-x}$ $x=5\%$	#2
250 nm $\text{Si}_x\text{Ge}_{1-x}$ $x=0-5\%$	
600 nm Ge	#1
substrate Si(111)	



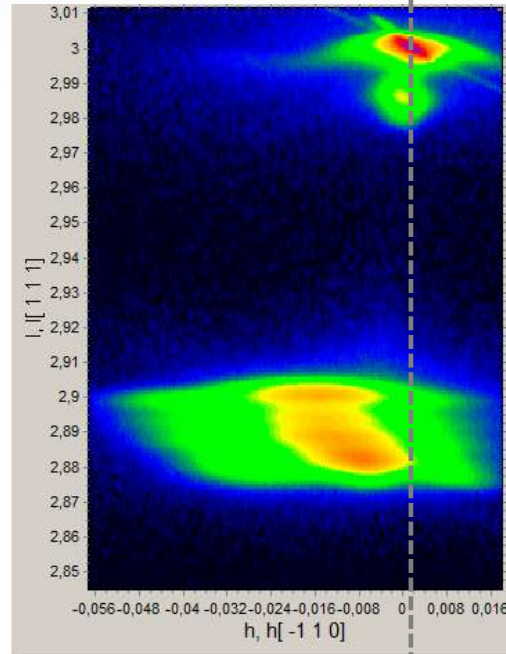
Extract miscut
for each SiGe layer

RSM from a SiGe graded heterostructure: Miscut, Relaxation and Concentration



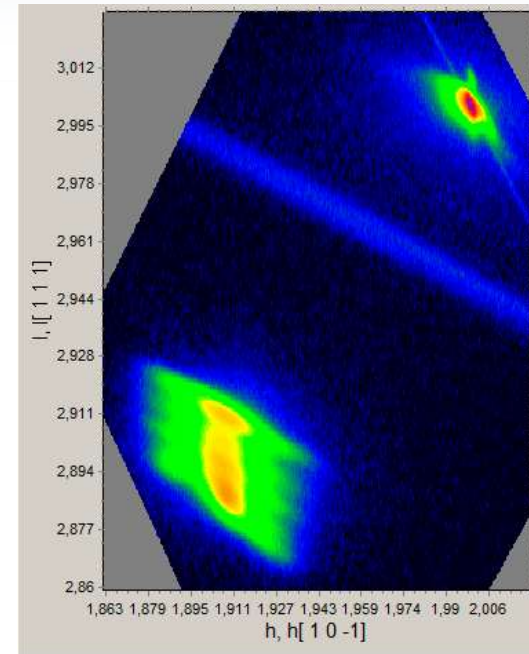
500 nm $\text{Si}_x\text{Ge}_{1-x}$ $x=20\%$
250 nm $\text{Si}_x\text{Ge}_{1-x}$ $x=15-20\%$
250 nm $\text{Si}_x\text{Ge}_{1-x}$ $x=15\%$
250 nm $\text{Si}_x\text{Ge}_{1-x}$ $x=10-15\%$
250 nm $\text{Si}_x\text{Ge}_{1-x}$ $x=10\%$
250 nm $\text{Si}_x\text{Ge}_{1-x}$ $x=5-10\%$
250 nm $\text{Si}_x\text{Ge}_{1-x}$ $x=5\%$
250 nm $\text{Si}_x\text{Ge}_{1-x}$ $x=0-5\%$
600 nm Ge
substrate Si(111)

Si(333)



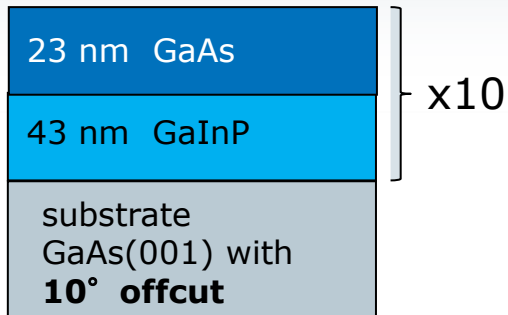
Extract miscut
for each SiGe layer

Si(531+)



Relaxation
Concentration

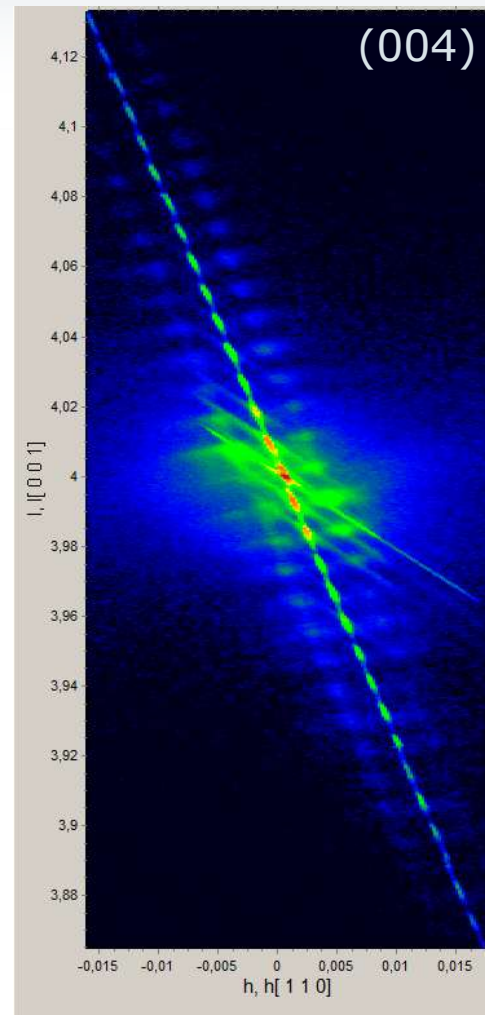
RSM from superlattices with large offcut



Sample courtesy of Uni Sheffield

Evaluated Parameters:

- Concentration
- Layer thickness
- SL period



RSM from superlattices with large offcut

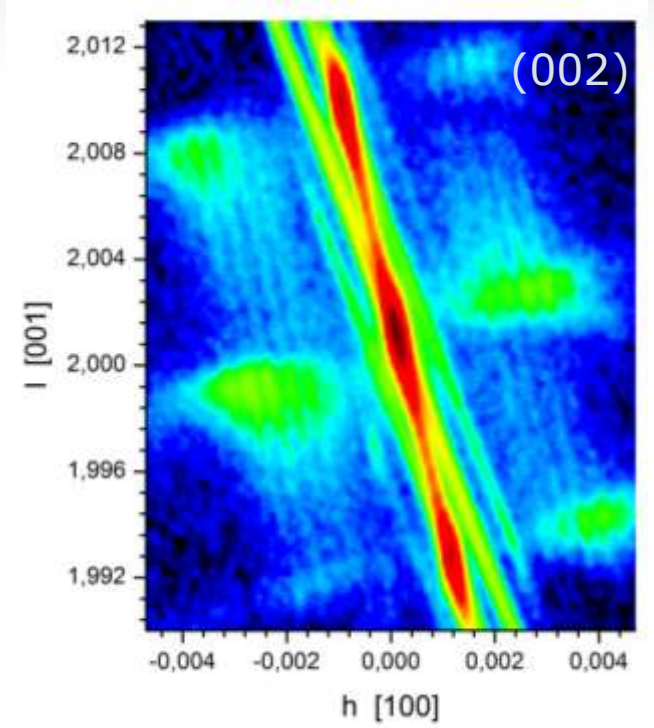
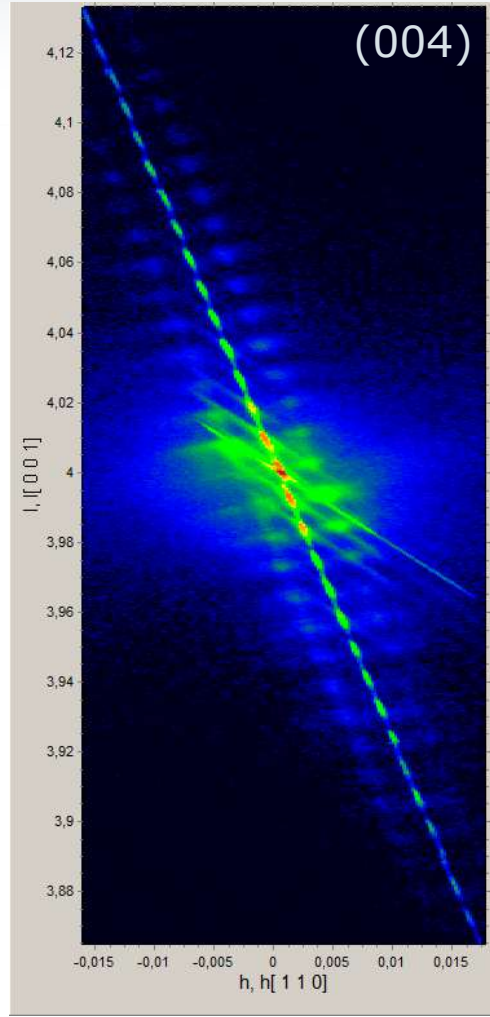


23 nm GaAs	} x10
43 nm GaInP	
substrate GaAs(001) with 10° offcut	

Sample courtesy of Uni Sheffield

Evaluated Parameters:

- Concentration
- Layer thickness
- SL period



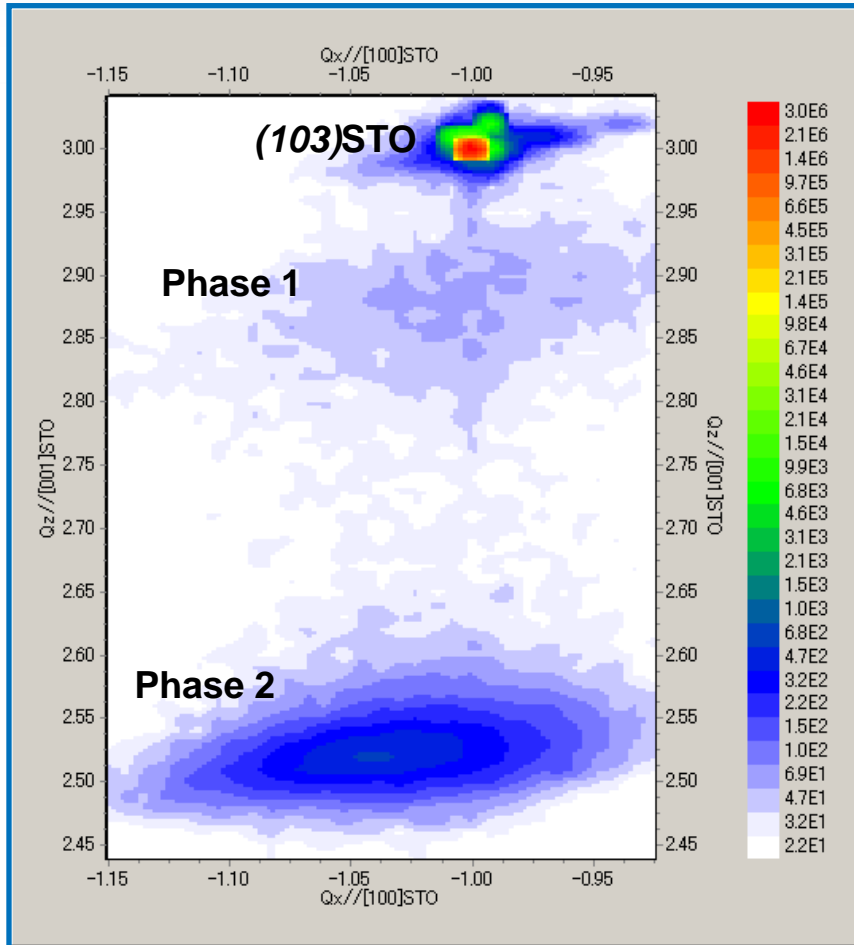
Periodic lateral structure due to substrate steps

Outline

- What is Reciprocal Space
- What can be measured by Reciprocal Space maps (RSMs)
- How to measure RSMs
- RSMs with 1D-detectors
- **RSMs with 2D-detectors**

Fast RSM with a 2D-detector

Example: $\text{BiFeO}_3(200\text{nm})/(001)\text{SrTiO}_3$



Scintillation Counter

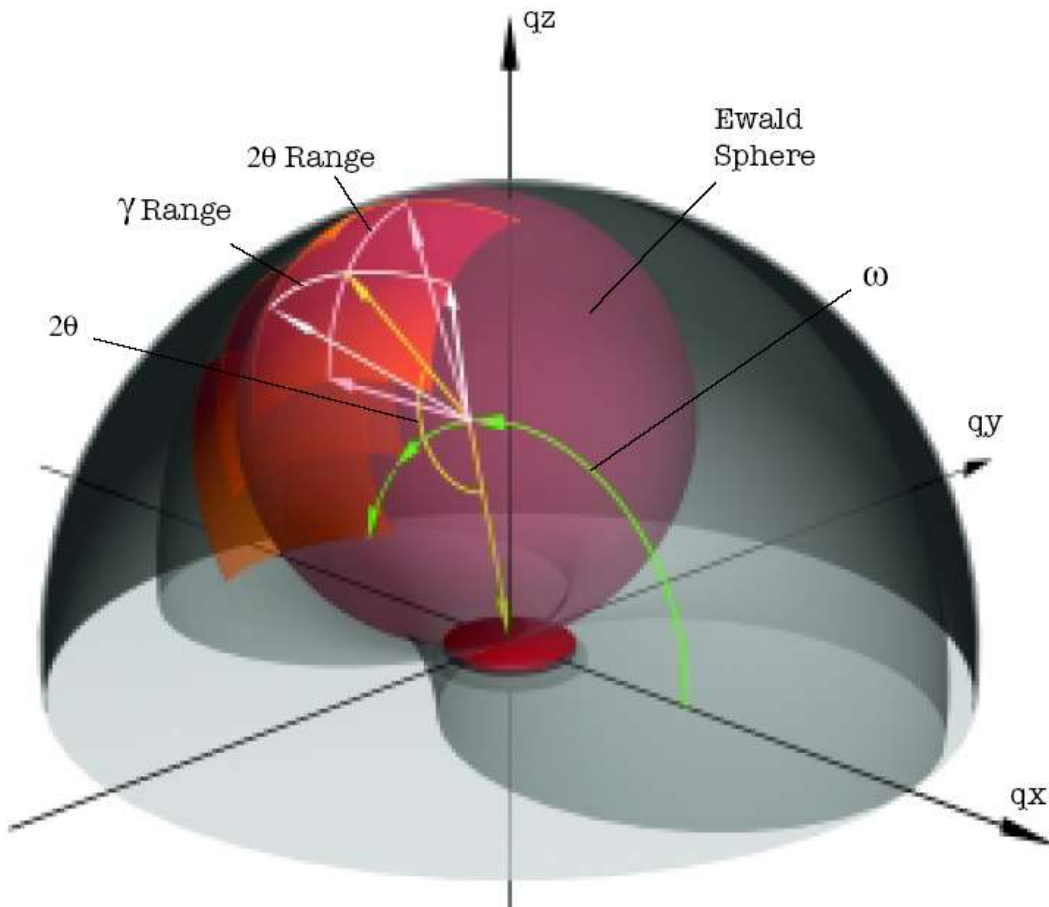
- Measurement time: 8 hours
- Just one (103) diffraction spot
- High resolution not needed

Fast RSM with a 2D-detector: The VANTEC-500



- Xe-based gas detector
- Window diameter of 140 mm
- 2048 x 2048 pixels with 68 x 68 μm size
- Detector noise <0.0005 cps/mm²
- 2 θ range
 - 23° at 300 mm
 - 56° at 100 mm

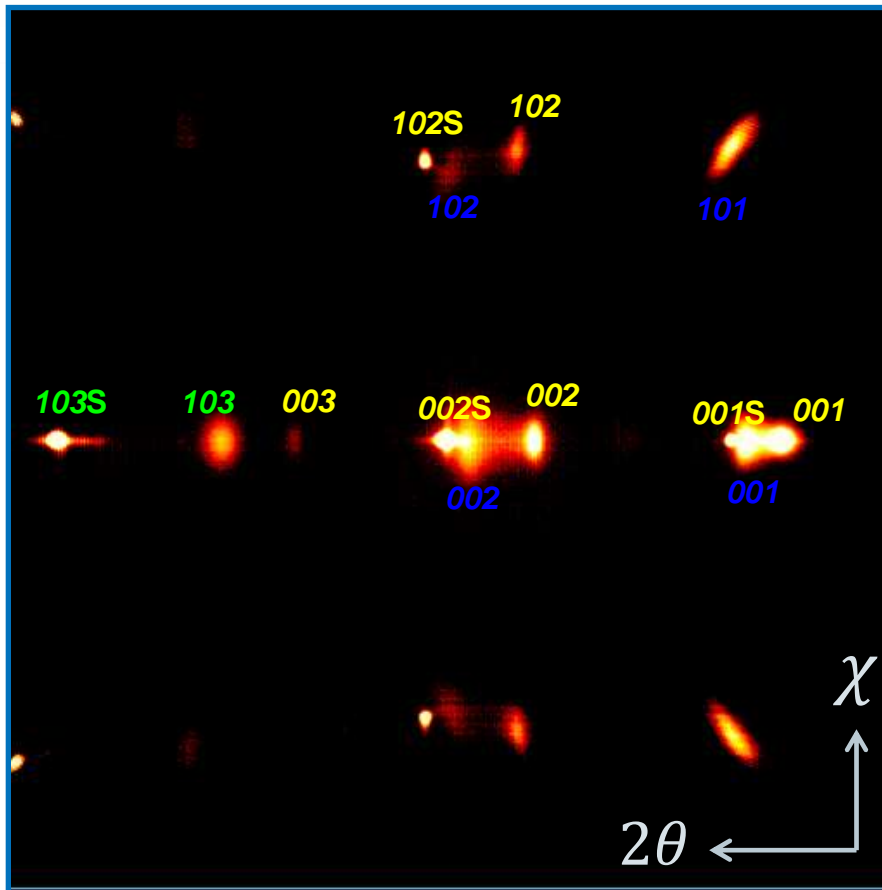
Fast RSM with a 2D-detector: Measurement mode



- 2D detector used in fixed position --> fixed range in 2θ and γ is measured simultaneously
- ω scanned for one frame for half of the 2θ range of the detector --> Ewald sphere (red) is rotated to integrate the reflection

Fast RSM with a 2D-detector

Example: $\text{BiFeO}_3(200\text{nm})/(001)\text{SrTiO}_3$

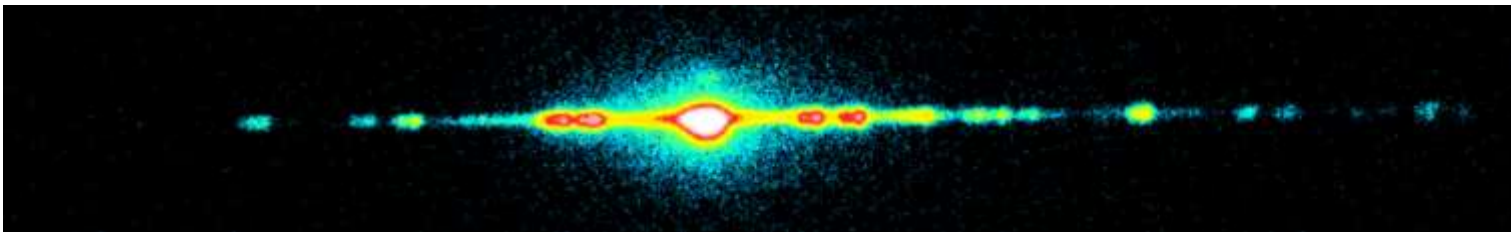


- Integration time ≈ 45 min
- In-plane epitaxial relation as well as existence of second phase (impurity phase) is clear.
- Sample from Osaka University

Benefits of RSM with 2D-detector

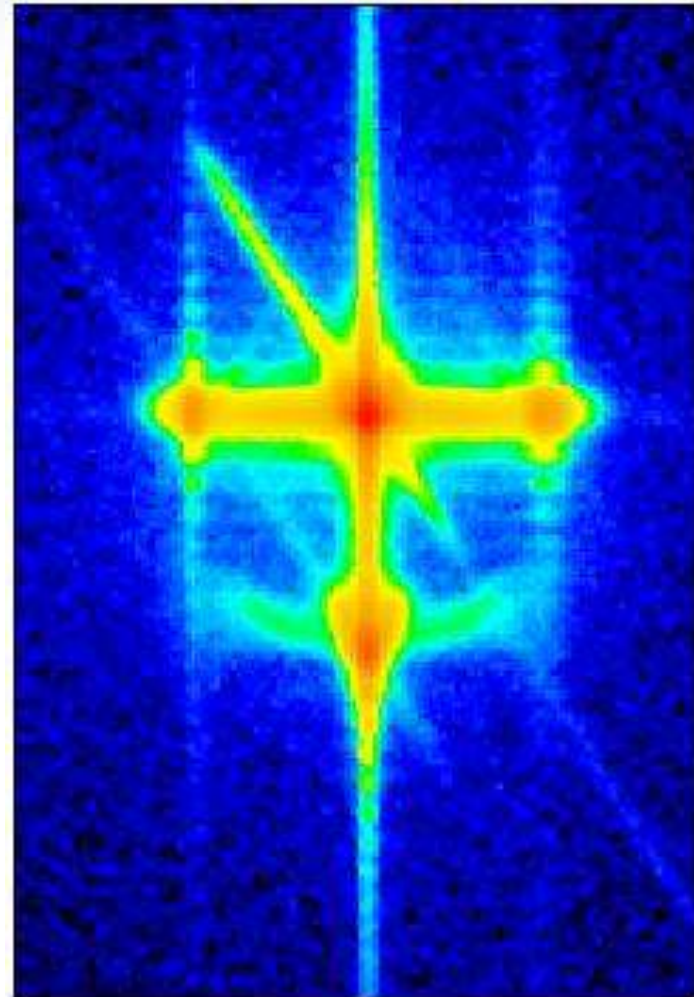


- Very fast, no alignment required
- Good indication of degree of orientation / quality of layers
- Do I have the layer structure that I want?
- Can spot certain sample-to-sample differences immediately
- Use it as a very fast feedback loop to optimize the making of your sample



Any Questions?

Please type any questions you may have in the **Q&A panel** and click **Send**.



Join us for X-TEAM Tour 2012

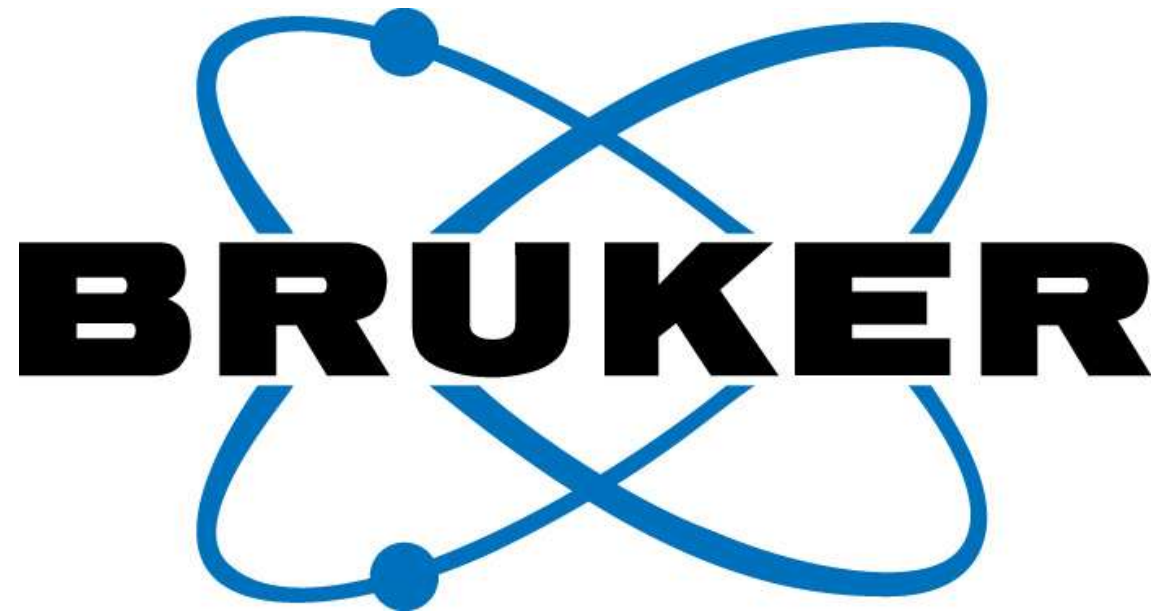


www.bruker-axs.com/xteamtour2012

- Educational one-day seminars on X-ray Analysis
- April – November in a city near you!
- Check the tour schedule and register early!



April	Vancouver, British Columbia - Monday, April 30
May	Seattle, Washington - Wednesday, May 2
	Portland, Oregon - Friday, May 4
	Toronto, Ontario, Canada - Monday, May 7
	Ottawa, Ontario, Canada - Wednesday, May 9
	Montreal, Quebec, Canada - Friday, May 11
August	Fremont, California - Monday, May 14
	Salt Lake City, Utah - Wednesday, May 16
	Denver, Colorado - Friday, May 18
November	Minneapolis, Minnesota - Monday, August 6
	St. Louis, Missouri - Wednesday, August 8
	Memphis, Tennessee - Friday, August 10
	Bethesda, Maryland - Monday, November 5
	New Brunswick, New Jersey - Wednesday, November 7
	New Haven, Connecticut - Friday, November 9



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